

TL03x, TL03xA, TL03xY ENHANCED-JFET LOW-POWER LOW-OFFSET OPERATIONAL AMPLIFIERS

SLOS180B – FEBRUARY 1997 – REVISED FEBRUARY 1999

- Direct Upgrades for the TL06x Low-Power BiFETs
- Low Power Consumption . . . 6.5 mW/Channel Typ
- On-Chip Offset-Voltage Trimming for Improved DC Performance (1.5 mV, TL031A)
- Higher Slew Rate and Bandwidth Without Increased Power Consumption
- Available in TSSOP for Small Form-Factor Designs

description

The TL03x series of JFET-input operational amplifiers offer improved dc and ac characteristics over the TL06x family of low-power BiFET operational amplifiers. On-chip zener trimming of offset voltage yields precision grades as low as 1.5 mV (TL031A) for greater accuracy in dc-coupled applications. Texas Instruments improved BiFET process and optimized designs also yield improved bandwidths and slew rates without increased power consumption. The TL03x devices are pin-compatible with the TL06x and can be used to upgrade existing circuits or for optimal performance in new designs.

BiFET operational amplifiers offer the inherently higher input impedance of the JFET-input transistors without sacrificing the output drive associated with bipolar amplifiers. This higher input impedance makes the TL3x amplifiers better suited for interfacing with high-impedance sensors or very low-level ac signals. These devices also feature inherently better ac response than bipolar or CMOS devices having comparable power consumption.

The TL03x family has been optimized for micropower operation, while improving on the performance of the TL06x series. Designers requiring significantly faster ac response should consider the Excalibur TLE206x family of low-power BiFET operational amplifiers.

Because BiFET operational amplifiers are designed for use with dual power supplies, care must be taken to observe common-mode input-voltage limits and output swing when operating from a single supply. DC biasing of the input signal is required and loads should be terminated to a virtual-ground node at midsupply. Texas Instruments TLE2426 integrated virtual-ground generator is useful when operating BiFET amplifiers from single supplies.

The TL03x devices are fully specified at ± 15 V and ± 5 V. For operation in low-voltage and/or single-supply systems, Texas Instruments LinCMOS families of operational amplifiers (TLC-prefix) are recommended. When moving from BiFET to CMOS amplifiers, particular attention should be paid to slew rate, bandwidth requirements, and output loading.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from –40°C to 85°C. The M-suffix devices are characterized for operation over the full military temperature range of –55°C to 125°C.



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 **TEXAS
INSTRUMENTS**

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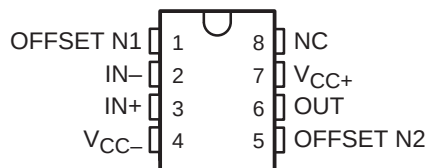
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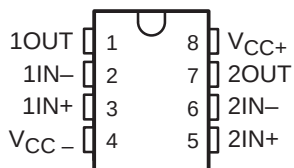
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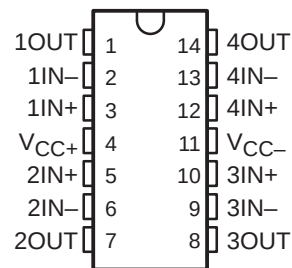
TL031x, TL031Ax
D, JG, OR P PACKAGE
(TOP VIEW)



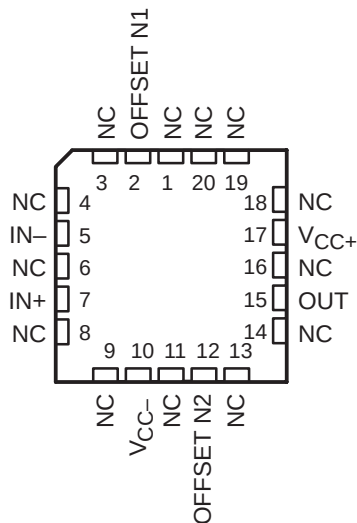
TL032x, TL032Ax
D, JG, OR P PACKAGE
(TOP VIEW)



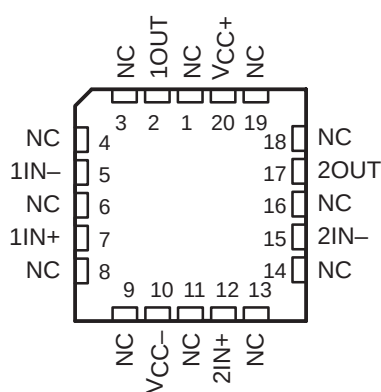
TL034x, TL034Ax
D, J, N, OR PW PACKAGE
(TOP VIEW)



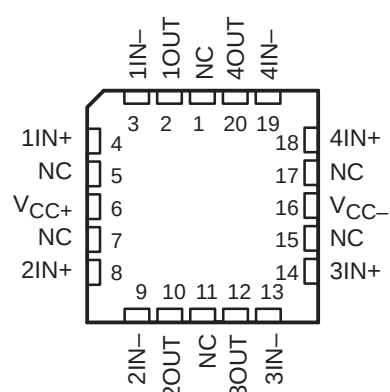
TL031M, TL031AM
FK PACKAGE
(TOP VIEW)



TL032M, TL032AM
FK PACKAGE
(TOP VIEW)



TL034M, TL034AM
FK PACKAGE
(TOP VIEW)



NC – No internal connection

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AVAILABLE OPTIONS

T _A	V _{IO} MAX AT 25°C	PACKAGED DEVICES							CHIP FORM‡ (Y)
		SMALL OUTLINE† (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	CERAMIC DIP (JG)	PLASTIC DIP (N)	PLASTIC DIP (P)	TSSOP† (PW)	
0°C to 70°C	0.8 mV	TL031ACD TL032ACD	—	—	—	—	TL031ACP TL032ACP	—	TL031Y TL032Y TL034Y
	1.5 mV	TL031CD TL032CD TL034ACD	—	—	—	TL034ACN	TL031CP TL032CP	—	
	4 mV	TL034CD	—	—	—	TL034CN	—	TL034CPW	
–40°C to 85°C	0.8 mV	TL031AID TL032AID	—	—	—	—	TL031AIP TL032AIP	—	—
	1.5 mV	TL031ID TL032ID TL034AID	—	—	—	TL034AIN	TL031IP TL032IP	—	—
	4 mV	TL034ID	—	—	—	TL034IN	—	—	—
–55°C to 125°C	0.8 mV	TL031AMD TL032AMD	TL031AMFK TL032AMFK	—	TL031AMJG TL032AMJG	—	TL031AMP TL032AMP	—	—
	1.5 mV	TL031MD TL032MD TL034AMD	TL031MFK TL032MFK TL034AMFK	TL034AMJ	TL031MJG TL032MJG	TL034AMN	TL031MP TL032MP	—	—
	4 mV	TL034MD	TL034MFK	TL034MJ	—	TL034MN	—	—	—

† The D and PW packages are available taped and reeled and are indicated by adding an R suffix to device type (e.g., TL034CDR or TL034CPWR).

‡ Chip forms are tested at 25°C.

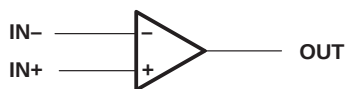
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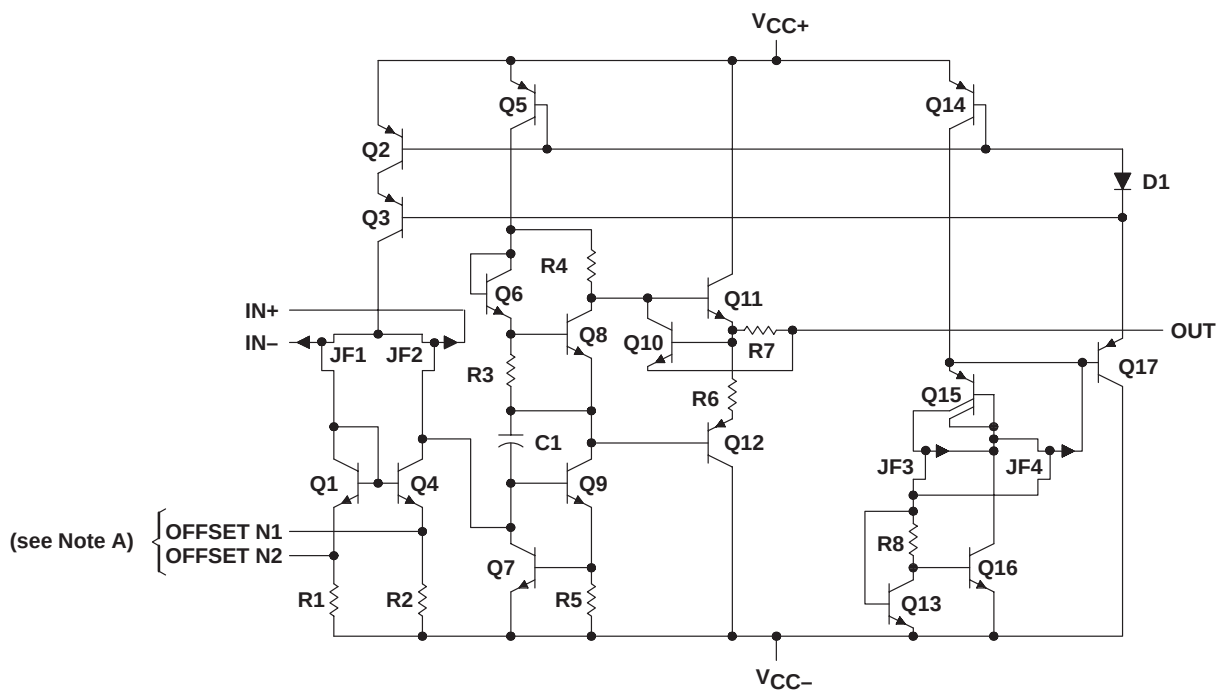
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symbol (each amplifier)



equivalent schematic (each amplifier)



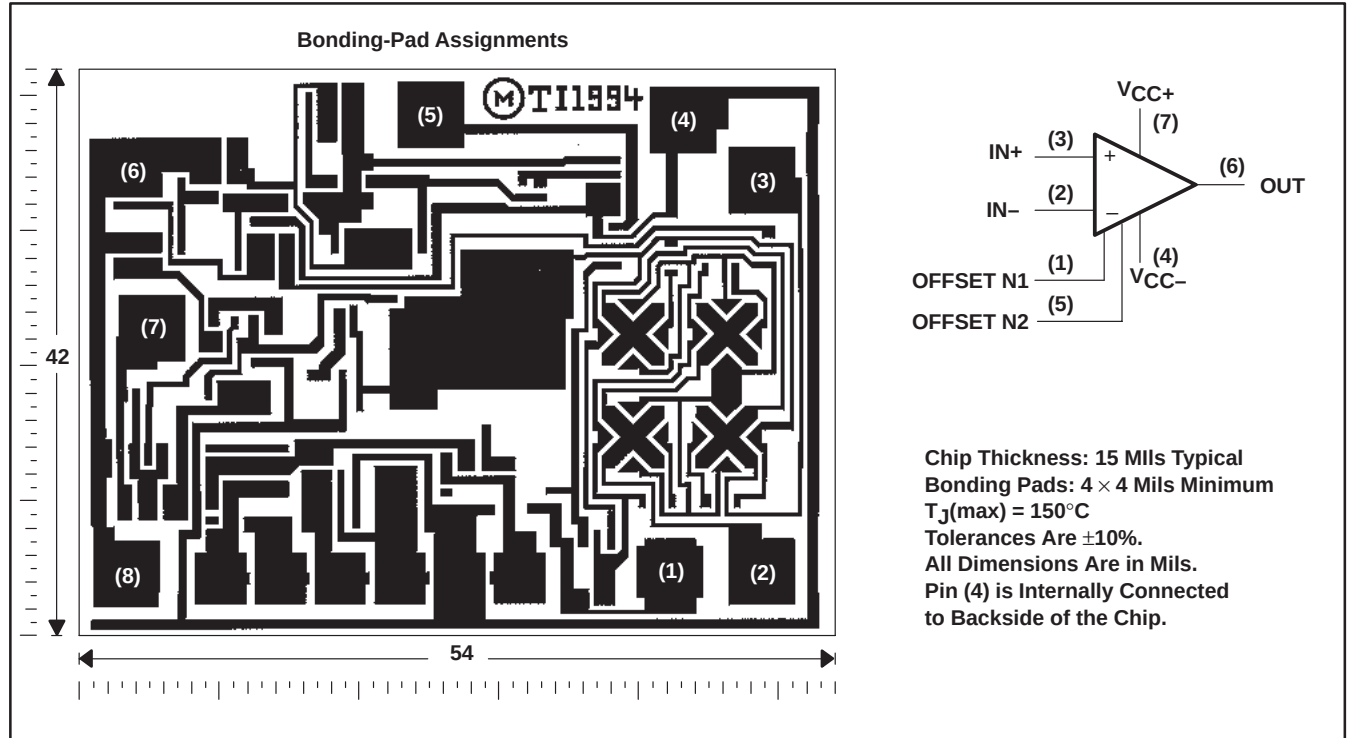
NOTE A: OFFSET N1 and OFFSET N2 are available only on the TL031.

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TL031Y chip information

This chip, when properly assembled, has characteristics similar to the TL031C. Thermal compression or ultrasonic bonding can be used on the doped-aluminum bonding pads. These chips can be mounted with conductive epoxy or a gold-silicon preform.

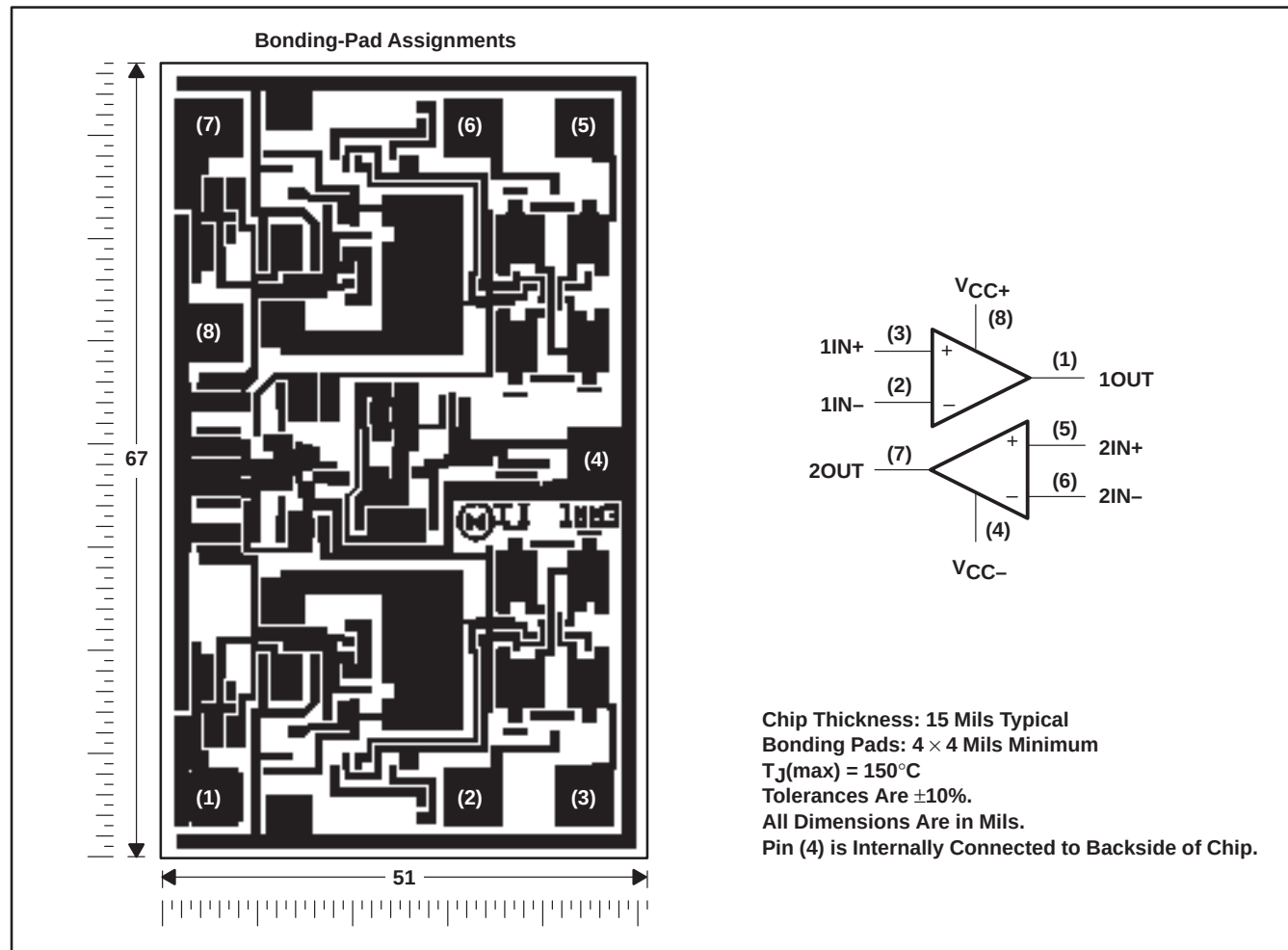


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TL032Y chip information

This chip, when properly assembled, has characteristics similar to the TL032C. Thermal compression or ultrasonic bonding can be used on the doped-aluminum bonding pads. These chips can be mounted with conductive epoxy or a gold-silicon preform.

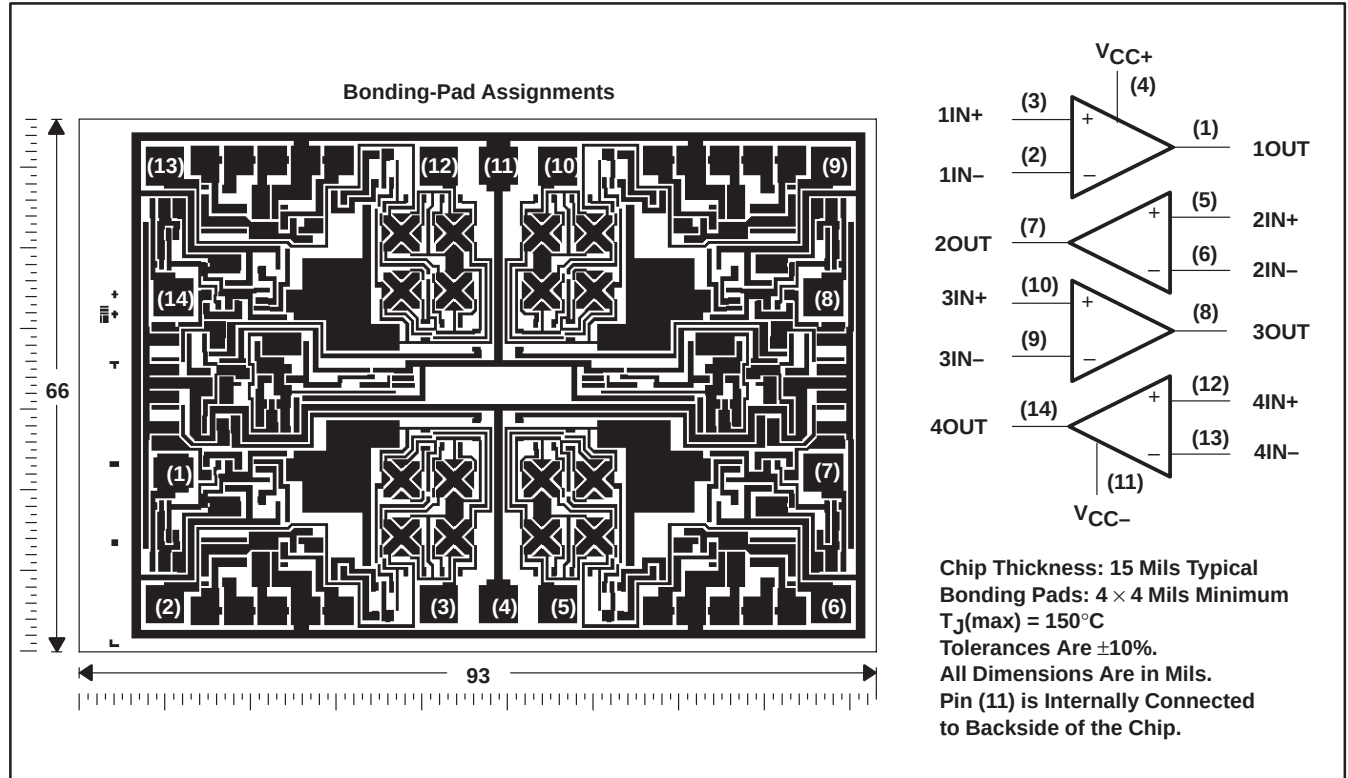


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TL034Y chip information

This chip, when properly assembled, has characteristics similar to the TL034C. Thermal compression or ultrasonic bonding can be used on the doped-aluminum bonding pads. These chips can be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V_{CC+} (see Note 1)	18 V
Supply voltage, V_{CC-} (see Note 1)	–18 V
Differential input voltage, V_{ID} (see Note 2)	±30 V
Input voltage, V_I (any input) (see Notes 1 and 3)	±15 V
Input current, I_I (each input)	±1 mA
Output current, I_O (each output)	±40 mA
Total current into V_{CC+}	160 mA
Total current out of V_{CC-}	160 mA
Duration of short-circuit current at (or below) 25°C (see Note 4)	Unlimited
Continuous total power dissipation	See Dissipation Rating Table
Storage temperature range, T_{stg}	–65°C to 150°C
Case temperature for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, N, P, or PW package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: J or JG package	300°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. All voltage values, except differential voltages, are with respect to the midpoint between V_{CC+} and V_{CC-} .
 2. Differential voltages are at $IN+$ with respect to $IN-$.
 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
 4. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING	$T_A = 125^\circ\text{C}$ POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	190 mW
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
J	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
N	1150 mW	9.2 mW/°C	736 mW	598 mW	230 mW
P	1100 mW	8.0 mW/°C	640 mW	520 mW	200 mW
PW	700 mW	5.6 mW/°C	448 mW	N/A	N/A

recommended operating conditions

		C SUFFIX		I SUFFIX		M SUFFIX		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Supply voltage, $V_{CC\pm}$		±5	±15	±5	±15	±5	±15	V
Common-mode input voltage, V_{IC}	$V_{CC\pm} = \pm 5\text{ V}$	–1.5	4	–1.5	4	–1.5	4	V
	$V_{CC\pm} = \pm 15\text{ V}$	–11.5	14	–11.5	14	–11.5	14	
Operating free-air temperature, T_A		0	70	–40	85	–55	125	°C



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TL031C and TL031AC electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031C, TL031AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031C	25°C	0.54 3.5		0.5 1.5		mV		
				Full range†	4.5		2.5				
			TL031AC	25°C	0.41 2.8		0.34 0.8				
				Full range†	3.8		1.8				
α _{VIO}	Temperature coefficient of input offset voltage		TL031C	25°C to 70°C	7.1		5.9		μV/°C		
			TL031AC	25°C to 70°C	7.1		5.9 25				
Input offset voltage long-term drift‡					25°C	0.04		0.04		μV/mo	
I _{IO}	Input offset current		V _O = 0, V _{IC} = 0, See Figure 5		25°C	1	100	1	100	pA	
		70°C			9	200	12	200			
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	2	200	2	200	pA		
				70°C	50	400	80	400			
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to .4		-11.5 to 14				
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				0°C	3	4.2	13	14			
				70°C	3	4.3	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				0°C	-3	-4.1	-12.5	-13.9			
				70°C	-3	-4.2	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				0°C	3	11.1	4	13.5			
				70°C	4	13.3	5	15.2			
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				0°C	70	87	75	94			
				70°C	70	87	75	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				0°C	75	96	75	96			
				70°C	75	96	75	96			

† Full range is 0°C to 70°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.



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TL031C and TL031AC electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL031C, TL031AC						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation	V _O = 0, No load	25°C		1.9	2.5		6.5	8.4	mW
		0°C		1.8	2.5		6.3	8.4	
		70°C		1.9	2.5		6.3	8.4	
I _{CC} Supply current	V _O = 0, No load	25°C		192	250		217	280	μA
		0°C		184	250		211	280	
		70°C		189	250		210	280	

TL031C and TL031AC operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031C, TL031AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain [†]	R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	2			1.5	2.9		V/μs	
			0°C	1.8			1	2.6			
			70°C	2.2			1.5	3.2			
SR–	Negative slew rate at unity gain [†]		25°C	3.9			1.5	5.1		V/μs	
			0°C	3.7			1.5	5			
			70°C	4			1.5	5			
t _r	Rise time	V _I (PP) = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	138			132			ns	
			0°C	134			127				
			70°C	150			142				
t _f	Fall time	V _I (PP) = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	138			132			ns	
			0°C	134			127				
			70°C	150			142				
Overshoot factor		V _I (PP) = ±10 mV, C _L = 100 pF, C _L = 100 pF, See Figures 1 and 2	25°C	11%			5%				
			0°C	10%			4%				
			70°C	12%			6%				
V _n	Equivalent input noise voltage	TL031C	R _S = 20 Ω, See Figure 3	f = 10 Hz	25°C	61			nV/√Hz		
				f = 1 kHz		41					
		TL031AC		f = 10 Hz	25°C	61					
				f = 1 kHz		41 60					
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003		pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4	25°C	1			1.1			MHz	
			0°C	1			1.1				
			70°C	1			1				
φ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4	25°C	61°			65°				
			0°C	61°			65°				
			70°C	60°			64°				

[†] For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V.

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TL031I and TL031AI electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031I, TL031AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031I	25°C	0.54		3.5	0.5		1.5	mV
				Full range†			5.3			3.3	
			TL031AI	25°C	0.41		2.8	0.34		0.8	
				Full range†			4.6			2.6	
αV _{IO}	Temperature coefficient of input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL031I	25°C to 85°C	6.5		6.2				μV/°C
			TL031AI	25°C to 85°C	6.5		6.2		25		
Input offset voltage long-term drift‡				25°C	0.04		0.04				μV/mo
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	1		100	1		100	pA
				85°C	0.02		0.45	0.02		0.45	nA
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	2		200	2		200	pA
				85°C	0.2		0.9	0.2		0.9	nA
V _{ICR}	Common-mode input voltage range			25°C	–1.5 to 4	–3.4 to 5.4	–11.5 to 14		–13.4 to 15.4	V	
				Full range†	–1.5 to 4	–11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13		14	V	
				–40°C	3	4.1	13		14		
				85°C	3	4.4	13		14		
V _{OM–}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	–3	–4.2	–12.5		–13.9	V	
				–40°C	–3	–4.1	–12.5		–13.8		
				85°C	–3	–4.2	–12.5		–14		
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5		14.3	V/mV	
				–40°C	3	8.4	4		11.6		
				85°C	4	13.5	5		15.3		
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75		94	dB	
				–40°C	70	87	75		94		
				85°C	70	87	75		94		
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75		96	dB	
				–40°C	75	96	75		96		
				85°C	75	96	75		96		

[†] Full range is –40°C to 85°C.

[‡] Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

[§] At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.

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TL031I and TL031AI electrical characteristics at specified free-air temperature (continued)

PARAMETER		TEST CONDITIONS		T _A	TL031I, TL031AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
P _D	Total power dissipation	V _O = 0,	No load	25°C	1.9		2.5	6.5		8.4	mW
				−40°C	1.4		2.5	5.4		8.4	
				85°C	1.9		2.5	6.2		8.4	
I _{CC}	Supply current	V _O = 0,	No load	25°C	192		250	217		280	μA
				−40°C	144		250	181		280	
				85°C	189		250	207		280	

TL031I and TL031AI operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031I, TL031AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ C _L = 100 pF, See Figure 1	25°C	2			1.5		2.9		V/μs
			−40°C	1.6			1		2.1		
			85°C	2.3			1.5		3.3		
SR−	Negative slew rate at unity gain†		25°C	3.9			1.5		5.1		V/μs
			−40°C	3.3			1.5		4.8		
			85°C	4.1			1.5		4.9		
t _r	Rise time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	138			132			ns	
		−40°C	132			123					
		85°C	154			146					
t _f	Fall time	V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	138			132			ns	
		−40°C	132			123					
		85°C	154			146					
Overshoot factor		V _{I(PP)} = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	11%			5%				
			−40°C	12%			5%				
			85°C	13%			7%				
V _n	Equivalent input noise voltage	TL031I	R _S = 20 Ω, See Figure 3	f = 10 Hz	25°C	61			61		nV/√Hz
				f = 1 kHz		41			41		
		TL031AI	f = 10 Hz	25°C	61			61			
			f = 1 kHz		41			41 60			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003		pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV C _L = 25 pF, R _L = 10 kΩ, See Figure 4	25°C	1			1.1			MHz	
			−40°C	1			1.1				
			85°C	0.9			1				
ϕ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF R _L = 10 kΩ, See Figure 4	25°C	61°			65°				
			−40°C	60°			65°				
			85°C	60°			64°				

[†] For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V.

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TL031M and TL031AM electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031M, TL031AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	TL031M	25°C	0.54		3.5	0.5		1.5	mV	
			Full range†	6.5		4.5					
			TL031AM	25°C	0.41		2.8	0.34			0.8
				Full range†	5.8		3.8				
α _{VIO}	Temperature coefficient of input offset voltage	TL031M	25°C to 125°C	5.1		4.3		μV/°C			
		TL031AM	25°C to 125°C	5.1		4.3					
Input offset voltage long-term drift‡			25°C	0.04		0.04		μV/mo			
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0, See Figure 5	25°C	1	100	1	100	pA			
			125°C	0.2	10	0.2	10	nA			
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5	25°C	2	200	2	200	pA			
			125°C	7	20	8	20	nA			
V _{ICR}	Common-mode input voltage range		25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V			
			Full range†	-1.5 to 4		-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ	25°C	3	4.3	13	14	V			
			-55°C	3	4.1	13	14				
			125°C	3	4.4	13	14				
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	-3	-4.2	-12.5	-13.9	V			
			-55°C	-3	-4	-12.5	-13.8				
			125°C	-3	-4.3	-12.5	-14				
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ	25°C	4	12	5	14.3	V/mV			
			-55°C	3	7.1	4	10.4				
			125°C	3	12.9	4	15				
r _i	Input resistance		25°C	10 ¹²		10 ¹²		Ω			
c _i	Input capacitance		25°C	5		4		pF			
CMR _R	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω	25°C	70	87	75	94	dB			
			-55°C	70	87	70	94				
			125°C	70	87	70	94				
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω	25°C	75	96	75	96	dB			
			-55°C	75	96	75	95				
			125°C	75	96	75	96				
P _D	Total power dissipation	V _O = 0, No load	25°C	1.9	2.5	6.5	8.4	mW			
			-55°C	1.1	2.5	4.7	8.4				
			125°C	1.8	2.5	5.8	8.4				

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.



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TL031M and TL031AM electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL031M, TL031AM						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
I _{CC} Supply current	V _O = 0, No load	25°C		192	250		217	280	μA
		–55°C		114	250		156	280	
		125°C		178	250		197	280	

TL031M and TL031AM operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL031M, TL031AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain [†]	R _L = 10 kΩ, C _L = 100 pF, See Figure 1		25°C	2			1.5	2.9	V/μs	
				–55°C	1.4			1	1.9		
				125°C	2.4			1	3.5		
SR–	Negative slew rate at unity gain [†]			25°C	3.9			1.5	5.1	V/μs	
				–55°C	3.2			1	4.6		
				125°C	4.1			1	4.7		
t _r	Rise time	V _I (PP) = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2		25°C	138			132		ns	
				–55°C	142			123			
				125°C	166			158			
t _f	Fall time	V _I (PP) = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figure 1		25°C	138			132		ns	
				–55°C	142			123			
				125°C	166			158			
Overshoot factor		V _I (PP) = ±10 mV, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2		25°C	11%			5%			
				–55°C	16%			6%			
				125°C	14%			8%			
V _n	Equivalent input noise voltage	TL031M	R _S = 20 Ω, See Figure 3	f = 10 Hz	25°C	61			61		nV/√Hz
				f = 1 kHz		41			41		
		TL031AM		f = 10 Hz	25°C	61			61		
				f = 1 kHz		41			41		
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003		pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4		25°C	1			1.1		MHz	
				–55°C	1			1.1			
				125°C	0.9			0.9			
φ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4		25°C	61°			65°			
				–55°C	57°			64°			
				125°C	59°			62°			

[†] For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V.



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TL031Y electrical characteristics, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		TL031Y						UNIT
				V _{CC±} = ±5 V			V _{CC±} = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, R _S = 50 Ω	V _{IC} = 0,	0.54			0.5			mV
α _{VIO}	Temperature coefficient of input offset voltage			7.1			5.9			μV/°C
I _{IO}	Input offset current	V _O = 0, See Figure 5	V _{IC} = 0,	1			1			pA
I _{IB}	Input bias current			2			2			pA
V _{ICR}	Common-mode input voltage range			–3.4 to 5.4			–13.4 to 15.4			V
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		4.3			14			V
V _{OM–}	Maximum negative peak output voltage swing	R _L = 10 kΩ		–4.2			–13.9			V
A _{VD}	Large-signal differential voltage amplification†	R _L = 10 kΩ		12			14.3			V/mV
r _i	Input resistance			10 ¹²			10 ¹²			Ω
c _i	Input capacitance			5			4			pF
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , R _S = 50 Ω	V _O = 0,	87			94			dB
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0,	R _S = 50 Ω	96			96			dB
P _D	Total power dissipation	V _O = 0,	No load	1.9			6.5			mW
I _{CC}	Supply current			192			217			μA

† At $V_{CC\pm} = \pm 5\text{ V}$, $V_O = \pm 2.3\text{ V}$; at $V_{CC\pm} = \pm 15\text{ V}$, $V_O = \pm 10\text{ V}$.

TL031Y operating characteristics, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		TL031Y						UNIT
				V _{CC±} = ±5 V			V _{CC±} = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain‡	R _L = 10 kΩ, C _L = 100 pF, See Figure 1	R _L = 10 kΩ, C _L = 100 pF, See Figure 1	2			2.9			V/μs
SR–	Negative slew rate at unity gain‡			3.9			5.1			V/μs
t _r	Rise time	V _{I(PP)} = ±10 mV,		138			132			ns
t _f	Fall time	R _L = 10 kΩ, C _L = 100 pF,		138			132			ns
Overshoot factor		See Figures 1 and 2		11%			5%			
V _n	Equivalent input noise voltage	R _S = 20 Ω, See Figure 3	f = 10 Hz	61			61			nV/√Hz
			f = 1 kHz	41			41			
I _n	Equivalent input noise current	f = 1 kHz		0.003			0.003			pA/√Hz
B ₁	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF,	R _L = 10 kΩ, See Figure 4	1			1.1			MHz
φ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF,	R _L = 10 kΩ, See Figure 4	61°			65°			

‡ For $V_{CC\pm} = \pm 5\text{ V}$, $V_{I(PP)} = \pm 1\text{ V}$; for $V_{CC\pm} = \pm 15\text{ V}$, $V_{I(PP)} = \pm 5\text{ V}$.



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TL032C and TL032AC electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032C, TL032AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032C	25°C	0.69	3.5	0.57	1.5	mV		
				Full range†	4.5	2.5					
			TL032AC	25°C	0.53	2.8	0.39	0.8			
				Full range†	3.8	1.8					
α _{VIO}	Temperature coefficient of input offset voltage		TL032C	25°C to 70°C	11.5	10.8	μV/°C				
			TL032AC	25°C to 70°C	11.5	10.8		25			
Input offset voltage long-term drift‡				25°C	0.04	0.04	μV/mo				
I _{IO}	Input offset current		V _O = 0, See Figure 5	V _{IC} = 0,	25°C	1	100	1	100	pA	
		70°C			9	200	12	200			
I _{IB}	Input bias current	V _O = 0, See Figure 5	V _{IC} = 0,	25°C	2	200	2	200	pA		
				70°C	50	400	80	400			
V _{ICR}	Common-mode input voltage range			25°C	–1.5 to 4	–3.4 to 5.4	–11.5 to 14	–13.4 to 15.4	V		
				Full range†	–1.5 to 4	–11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				0°C	3	4.2	13	14			
				70°C	3	4.3	13	14			
V _{OM–}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	–3	–4.2	–12.5	–13.9	V		
				0°C	–3	–4.1	–12.5	–13.9			
				70°C	–3	–4.2	–12.5	–14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				0°C	3	11.1	4	13.5			
				70°C	4	13.3	5	15.2			
r _i	Input resistance			25°C	10 ¹²	10 ¹²	Ω				
c _i	Input capacitance			25°C	5	14	pF				
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				0°C	70	87	75	94			
				70°C	70	87	75	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				0°C	75	96	75	96			
				70°C	75	96	75	96			

† Full range is 0°C to 70°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = 2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.



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TL032C and TL032AC electrical characteristics at specified free-air temperature (continued)

PARAMETER		TEST CONDITIONS		T _A	TL032C, TL032AC						UNIT		
					V _{CC±} = ±5 V			V _{CC±} = ±15 V					
					MIN	TYP	MAX	MIN	TYP	MAX			
P _D	Total power dissipation (two amplifiers)	V _O = 0,	No load	25°C	3.8			5	13			17	mW
				0°C	3.7			5	12.7			17	
				70°C	3.8			5	12.6			17	
I _{CC}	Supply current (two amplifiers)	V _O = 0,	No load	0°C	368			500	422			560	μA
				70°C	378			500	420			560	
V _{O1} /V _{O2}	Crosstalk attenuation	A _{VD} = 100 dB		25°C	120				120				dB

TL032C and TL032AC operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032C, TL032AC						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF, See Figure 1		25°C	12			1.5		2.9		V/μs
				0°C	1.8			1		2.6		
				70°C	2.2			1.5		3.2		
SR−	Negative slew rate at unity gain†			25°C	3.9			1.5		5.1		V/μs
				0°C	3.7			1.5		5		
				70°C	4			1.5		5		
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2		25°C	138			132			ns	
				0°C	134			127				
				70°C	150			142				
t _f	Fall time			25°C	138			132			ns	
				0°C	134			127				
				70°C	150			142				
Overshoot factor				25°C	11%			5%				
				0°C	10%			4%				
				70°C	12%			6%				
V _n	Equivalent input noise voltage	TL032C	f = 10 Hz	25°C	49			49			nV/√Hz	
			f = 1 kHz		41			41				
		TL032AC	f = 10 Hz	25°C	49			49				
			f = 1 kHz		41			41 60				
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4		25°C	1			1.1			MHz	
				0°C	1			1.1				
				70°C	1			1				
φ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4		25°C	61°			65°				
				0°C	61°			65°				
				70°C	60°			64°				

[†] For V_{CC±} = ±5 V, V_{I(PP)} = ±1 V; for V_{CC±} = ±15 V, V_{I(PP)} = ±5 V.

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TL032I and TL032AI electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032I, TL032AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	TL032I	25°C	0.69	3.5	0.57		1.5	mV		
			Full range†	5.3		3.3					
			TL032AI	25°C	0.53	2.8	0.39			0.8	
				Full range†	4.6		2.6				
α _{VIO}	Temperature coefficient of input offset voltage	TL032I	25°C to 85°C	11.4		10.8		μV/°C			
		TL032AI	25°C to 85°C	11.4		10.8 25					
Input offset voltage long-term drift‡			25°C	0.04		0.04		μV/mo			
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0, See Figure 5	25°C	1	100	1 100		pA			
			85°C	0.02	0.45	0.02 0.45		nA			
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5	25°C	2	200	2 200		pA			
			85°C	0.2	0.9	0.3 0.9		nA			
V _{ICR}	Common-mode input voltage range		25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14 -13.4 to 15.4		V			
			Full range†	-1.5 to 4		-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ	25°C	3	4.3	13 14		V			
			-40°C	3	4.2	13 14					
			85°C	3	4.4	13 14					
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ	25°C	-3	-4.2	-12.5 -13.9		V			
			-40°C	-3	-4.1	-12.5 -13.8					
			85°C	-3	-4.2	-12.5 -14					
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ	-40°C	3	8.4	4 11.6		V/mV			
			85°C	4	13.5	5 15.3					
r _i	Input resistance		25°C	10 ¹²		10 ¹²		Ω			
c _i	Input capacitance		25°C	5		4		pF			
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω	25°C	70	87	75 94		dB			
			-40°C	70	87	75 94					
			85°C	70	87	75 94					
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, V _O = 0, R _S = 50 Ω	25°C	75	96	75 96		dB			
			-40°C	75	96	75 96					
			85°C	75	96	75 96					

[†] Full range is -40°C to 85°C.

[‡] Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

[§] At V_{CC±} = ±5 V, V_O = 2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.

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TL032I and TL032AI electrical characteristics at specified free-air temperature (continued)

PARAMETER		TEST CONDITIONS		T _A	TL032I, TL032AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
P _D	Total power dissipation (two amplifiers)	V _O = 0,	No load	25°C	3.8		5	13		17	mW
				−40°C	2.9		5	10.9		17	
				85°C	3.7		5	12.4		17	
I _{CC}	Supply current (two amplifiers)	V _O = 0,	No load	25°C	384		500	434		560	μA
				−40°C	288		500	362		560	
				85°C	372		500	414		560	
V _{O1} /V _{O2}	Crosstalk attenuation	A _{VD} = 100 dB		25°C	120			120			dB

TL032I and TL032AI operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032I, TL032AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF	25°C	2			1.5	2.9		V/μs	
			−40°C	1.6			1	2.1			
			85°C	2.3			1.5	3.3			
SR−	Negative slew rate at unity gain†		25°C	3.9			1.5	5.1		V/μs	
			−40°C	3.3			1.5	4.8			
			85°C	4.1			1.5	4.9			
t _r	Rise time	V _I (PP) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	138			132			ns	
		−40°C	132			123					
		85°C	154			146					
t _f	Fall time	V _I (PP) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	138			132			ns	
		−40°C	132			123					
		85°C	154			146					
Overshoot factor		V _I (PP) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	11%			5%				
			−40°C	12%			5%				
			85°C	13%			7%				
V _n	Equivalent input noise voltage	TL032I	f = 10 Hz	25°C	49			49			nV/√Hz
			f = 1 kHz		41			41			
		TL032AI	f = 10 Hz	25°C	49			49			
			f = 1 kHz		41			41 60			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz
B ₁	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF,	R _L = 10 kΩ, See Figure 4	25°C	1			1.1			MHz
				−40°C	1			1.1			
				85°C	0.9			1			
φ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF,	R _L = 10 kΩ, See Figure 4	25°C	61°			65°			
				−40°C	61°			65°			
				85°C	60°			64°			

[†] For V_{CC±} = ±5 V, V_I(PP) = ±1 V; for V_{CC±} = ±15 V, V_I(PP) = ±5 V.



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TL032M and TL032AM electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032M, TL032AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL032M	25°C	0.69	3.5	0.57	1.5	mV		
				Full range†	6.5		4.5				
			TL032AM	25°C	0.53	2.8	0.39	0.8			
				Full range†	5.8		3.8				
α _{VIO}	Temperature coefficient of input offset voltage		TL032M	25°C to 125°C	9.7		9.7		μV/°C		
			TL032AM	25°C to 125°C	9.7		9.7				
Input offset voltage long-term drift‡				25°C	0.04		0.04		μV/mo		
I _{IO}	Input offset current		V _O = 0, See Figure 5	V _{IC} = 0,	25°C	1	100	1	100	pA	
		125°C			0.2	10	0.2	10	nA		
I _{IB}	Input bias current	V _O = 0, See Figure 5	V _{IC} = 0,	25°C	2	200	2	200	pA		
				125°C	7	20	8	20	nA		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
			Full range†	-1.5 to 4		-11.5 to 14					
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				-55°C	3	4.1	13	14			
				125°C	3	4.4	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				-55°C	-3	-4	-12.5	-13.8			
				125°C	-3	-4.3	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				-55°C	3	7.1	4	10.4			
				125°C	3	12.9	4	15			
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				-55°C	70	87	70	94			
				125°C	70	87	70	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _{CC±} = ±5 V to ±15 V, V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				-55°C	75	95	75	95			
				125°C	75	96	75	96			

[†] Full range is -55°C to 125°C.

[‡] Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

[§] At V_{CC±} = ±5 V, V_O = 2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.



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TL032M and TL032AM electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL032M, TL032AM						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers)	V _O = 0, No load	25°C		3.8	5		13	17	mW
		–55°C		2.3	5		9.4	17	
		125°C		3.6	5		11.8	17	
I _{CC} Supply current (two amplifiers)	V _O = 0, No load	25°C		384	500		434	560	μA
		–55°C		228	500		312	560	
		125°C		356	500		394	560	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100 dB	25°C		120			120		dB

TL032M and TL032AM operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL032M, TL032AM						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF, See and Figure 1		25°C	2			1.5 2.9			V/μs	
				–55°C	1.4			1 1.9				
				125°C	2.4			1 3.5				
SR–	Negative slew rate at unity gain†			25°C	3.9			1.5 5.1			V/μs	
				–55°C	3.2			1 4.6				
				125°C	4.1			1 4.7				
t _r	Rise time	V _I (pp) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2		25°C	138			132			ns	
				–55°C	142			123				
				125°C	166			58				
t _f	Fall time	V _I (pp) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figure 1		25°C	138			132			ns	
				–55°C	142			123				
				125°C	166			158				
Overshoot factor		V _I (pp) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2		25°C	11%			5%				
				–55°C	16%			6%				
				125°C	14%			8%				
V _n	Equivalent input noise voltage	TL032M	R _S = 20 Ω, See Figure 3	f = 10 Hz	25°C	49			49			nV/√Hz
				f = 1 kHz		41			41			
		TL032AM		f = 10 Hz	25°C	49			49			
				f = 1 kHz		41			41			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz	
B1	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4		25°C	1			1.1			MHz	
				–55°C	1			1.1				
				125°C	0.9			0.9				
φ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4		25°C	61°			65°				
				–55°C	57°			64°				
				125°C	59°			62°				

[†] For V_{CC±} = ±5 V, V_I(PP) = ±1 V; for V_{CC±} = ±15 V, V_I(PP) = ±5 V.



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TL032Y electrical characteristics, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	TL032Y						UNIT
			VCC± = ±5 V			VCC± = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
VIO	Input offset voltage	VO = 0, V IC = 0, RS = 50 Ω	0.69			0.57			mV
αVIO	Temperature coefficient of input offset voltage		11.5			10.8			μV/°C
IIO	Input offset current	VO = 0, V IC = 0, See Figure 5	1			1			pA
IIB	Input bias current	VO = 0, V IC = 0, See Figure 5	2			2			pA
VICR	Common-mode input voltage range		−3.4 to 5.4			−13.4 to 15.4			V
VOM+	Maximum positive peak output voltage swing	RL = 10 kΩ	4.3			14			V
VOM−	Maximum negative peak output voltage swing	RL = 10 kΩ	−4.2			−13.9			V
AVD	Large-signal differential voltage amplification†	RL = 10 kΩ	12			14.3			V/mV
ri	Input resistance		1012			1012			Ω
ci	Input capacitance		5			14			pF
CMRR	Common-mode rejection ratio	VIC = VICRmin, VO = 0, RS = 50 Ω	87			94			dB
kSVR	Supply-voltage rejection ratio (ΔVCC±/ΔVIO)	VCC± = ±5 V to ±15 V, VO = 0, RS = 50 Ω	96			96			dB
PD	Total power dissipation (two amplifiers)	VO = 0, No load	3.8			13			mW
VO1/VO2	Crosstalk attenuation	AVD = 100 dB	120			120			dB

† At $V_{CC\pm} = \pm 5\text{ V}, V_O = 2.3\text{ V}$; at $V_{CC\pm} = \pm 15\text{ V}, V_O = \pm 10\text{ V}$.

TL032Y operating characteristics, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		TL032Y						UNIT
				V _{CC±} = ±5 V			V _{CC±} = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF,		12			2.9			V/μs
SR–	Negative slew rate at unity gain†	See Figure 1 and Note 8		3.9			5.1			V/μs
t _r	Rise time	V _I (PP) = ±10 V,		138			132			ns
t _f	Fall time	R _L = 10 kΩ,, C _L = 100 pF,		138			132			ns
Overshoot factor		See Figures 1 and 2		11%			5%			
V _n	Equivalent input noise voltage	R _S = 20 Ω, See Figure 3	f = 10 Hz	49			49			nV/√Hz
			f = 1 kHz	41			41			
I _n	Equivalent input noise current	f = 1 kHz		0.003			0.003			pA/√Hz
B ₁	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF,	R _L = 10 kΩ, See Figure 4	1			1.1			MHz
φ _m	Phase margin at unity gain	V _I = 10 mV, C _I = 25 pF,	R _L = 10 kΩ, See Figure 4	61°			65°			

† For $V_{CC\pm} = \pm 5\text{ V}, V_{I(PP)} = \pm 1\text{ V}$; for $V_{CC\pm} = \pm 15\text{ V}, V_{I(PP)} = \pm 5\text{ V}$.



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TL034C and TL034AC electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034C, TL034AC						UNIT		
					V _{CC±} = ±5 V			V _{CC±} = ±15 V					
					MIN	TYP	MAX	MIN	TYP	MAX			
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034C	25°C	0.91		6		0.79		4		mV
				Full range†			8.2		6.2				
			TL034AC	25°C	0.7		3.5		0.58		1.5		
				Full range†			5.7		3.7				
α _{VIO}	Temperature coefficient of input offset voltage		TL034C	25°C to 70°C	11.6				12				μV/°C
			TL034AC	25°C to 70°C	11.6				12		25		
Input offset voltage long-term drift‡				25°C	0.04				0.04				μV/mo
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	1		100		1		100		pA
				70°C	9		200		12		200		
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	2		200		2		200		pA
				70°C	50		400		80		400		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4		-3.4 to 5.4		-11.5 to 14		-13.4 to 15.4		V
				Full range†	-1.5 to 4				-11.5 to 14				
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3		4.3		13		14		V
				0°C	3		4.2		13		14		
				70°C	3		4.3		13		14		
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3		-4.2		-12.5		-13.9		V
				0°C	-3		-4.1		-12.5		-13.9		
				70°C	-3		-4.2		-12.5		-14		
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4		12		5		14.3		V/mV
				0°C	3		11.1		4		13.5		
				70°C	4		13.3		5		15.2		
r _i	Input resistance			25°C	10 ¹²				10 ¹²				Ω
c _i	Input capacitance			25°C	5				14				pF
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70		87		75		94		dB
				0°C	70		87		75		94		
				70°C	70		87		75		94		
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75		96		75		96		dB
				0°C	75		96		75		96		
				70°C	75		96		75		96		

† Full range is 0°C to 70°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.

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TL034C and TL034AC electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL034C, TL034AC						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers)	V _O = 0, No load	25°C	7.7 10			26 34			mW
		0°C	7.4 10			25.3 34			
		70°C	7.6 10			25.2 34			
I _{CC} Supply current (four amplifiers)	V _O = 0, No load	25°C	0.77 1			0.87 1.12			mA
		0°C	0.74 1			0.85 1.12			
		70°C	0.76 1			0.84 1.12			
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100	25°C	120			120			dB

TL034C and TL034AC operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034C, TL034AC						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	2			1.5 2.9			V/μs	
			0°C	1.8			1 2.6				
			70°C	2.2			1.5 3.2				
SR–	Negative slew rate at unity gain†		25°C	3.9			1.5 5.1			V/μs	
			0°C	3.7			1.5 5				
			70°C	4			1.5 5				
t _r	Rise time	V _I (PP) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	138			132			ns	
			0°C	134			127				
			70°C	150			142				
t _f	Fall time	V _I (PP) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	138			132			ns	
			0°C	134			127				
			70°C	150			142				
Overshoot factor		V _I (PP) = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	11%			5%				
			0°C	10%			4%				
			70°C	12%			6%				
V _n	Equivalent input noise voltage	TL034C	R _S = 20 Ω, See Figure 3	f = 10 Hz	25°C	83			nV/√Hz		
				f = 1 kHz		43					
		TL034AC	f = 10 Hz	25°C	83						
			f = 1 kHz		43 60						
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003		pA/√Hz	
B ₁	Unity-gain bandwidth	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF, See Figure 4		25°C	1			1.1			MHz
				0°C	1			1.1			
				70°C	1			1			
ϕ _m	Phase margin at unity gain	V _I = 10 mV, R _L = 10 kΩ, C _L = 25 pF, See Figure 4		25°C	61°			65°			
				0°C	61°			65°			
				70°C	60°			64°			

† For V_{CC±} = ±5 V, V_I(PP) = ±1 V; for V_{CC±} = ±15 V, V_I(PP) = ±5 V.

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TL034I and TL034AI electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034I, TL034AI						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034I	25°C	0.91	3.6	0.79	4	mV		
				Full range†		9.3	7.3				
			TL034AI	25°C	0.7	3.5	0.58	1.5			
				Full range†		6.8	4.8				
α _{VIO}	Temperature coefficient of input offset voltage		TL034I	25°C to 85°C	11.5		11.6	μV/°C			
			TL034AI	25°C to 85°C	11.5		11.6		25		
Input offset voltage long-term drift‡				25°C	0.04		0.04		μV/mo		
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	1	100	1	100	pA		
				85°C	0.02	0.45	0.02	0.45	nA		
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	2	200	2	200	pA		
				85°C	0.2	0.9	0.3	0.9	nA		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to 4		-11.5 to 14				
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				-40°C	3	4.1	13	14			
				85°C	3	4.4	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				-40°C	-3	-4.1	-12.5	-13.8			
				85°C	-3	-4.2	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		-40°C	4	12	5	14.3	V/mV		
				85°C	3	8.4	4	11.6			
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				-40°C	70	87	75	94			
				85°C	70	87	75	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} / ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				-40°C	75	96	75	96			
				85°C	75	96	75	96			

[†] Full range is -40°C to 85°C.

[‡] Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

[§] At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.

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TL034I and TL034AI electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL034I, TL034AI						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (four amplifiers)	V _O = 0, No load	25°C		7.7	10		26	34	mW
		–40°C		5.8	10		21.7	34	
		85°C		7.4	10		24.8	34	
I _{CC} Supply current (four amplifiers)	V _O = 0, No load	25°C		0.77	1		0.87	1.12	mA
		–40°C		0.58	1		0.72	1.12	
		85°C		0.74	1		0.83	1.12	
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100	25°C		120			120		dB

TL034I and TL034AI operating characteristics

PARAMETER		TEST CONDITIONS		T _A	TL034I, TL034AI						UNIT	
					V _{CC±} = ±5 V			V _{CC±} = ±15 V				
					MIN	TYP	MAX	MIN	TYP	MAX		
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, See Figure 1	C _L = 100 pF,	25°C	2			1.5		2.9		V/μs
				−40°C	1.6			1		2.1		
				85°C	2.3			1.5		3.3		
SR−	Negative slew rate at unity gain†			25°C	3.9			1.5		5.1		V/μs
				−40°C	3.3			1.5		4.8		
				85°C	4.1			1.5		4.9		
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	138					132		ns	
			−40°C	132					123			
			85°C	154					146			
t _f	Fall time		25°C	138					132		ns	
			−40°C	132					123			
			85°C	154					146			
Overshoot factor			25°C	11%					5%			
			−40°C	12%					5%			
			85°C	13%					7%			
V _n	Equivalent input noise voltage	TL034I	f = 10 Hz	25°C	83			83		nV/√Hz		
			f = 1 kHz		43			43				
		TL034AI	f = 10 Hz	25°C	83			83				
			f = 1 kHz		43			43 60				
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003		pA/√Hz		
B ₁	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4	25°C	1			1.1		MHz			
			−40°C	1			1.1					
			85°C	0.9			1					
ϕ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4	25°C	61°			65°					
			−40°C	61°			65°					
			85°C	60°			64°					

† For $V_{CC\pm} = \pm 5 \text{ V}$, $V_{I(PP)} = \pm 1 \text{ V}$; for $V_{CC\pm} = \pm 15 \text{ V}$, $V_{I(PP)} = \pm 5 \text{ V}$.



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TL034M and TL034AM electrical characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034M, TL034AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	TL034M	25°C	0.91		3.6	0.78		4	mV
				Full range†			11			9	
			TL034AM	25°C	0.7		3.5	0.58		1.5	
				Full range†			8.5			6.5	
α _{VIO}	Temperature coefficient of input offset voltage	TL034M	25°C to 125°C	10.6		10.9				μV/°C	
			TL034AM	25°C to 125°C	10.6		10.9				
Input offset voltage long-term drift‡				25°C	0.04		0.04			μV/mo	
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	1	100	1	100	pA		
				125°C	0.2	10	0.2	10	nA		
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5		25°C	2	200	2	200	pA		
				125°C	7	20	8	20	nA		
V _{ICR}	Common-mode input voltage range			25°C	-1.5 to 4	-3.4 to 5.4	-11.5 to 14	-13.4 to 15.4	V		
				Full range†	-1.5 to 4		-11.5 to 14				
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ		25°C	3	4.3	13	14	V		
				-55°C	3	4.1	13	14			
				125°C	3	4.4	13	14			
V _{OM-}	Maximum negative peak output voltage swing	R _L = 10 kΩ		25°C	-3	-4.2	-12.5	-13.9	V		
				-55°C	-3	-4	-12.5	-13.8			
				125°C	-3	-4.3	-12.5	-14			
A _{VD}	Large-signal differential voltage amplification§	R _L = 10 kΩ		25°C	4	12	5	14.3	V/mV		
				-55°C	3	7.1	4	10.4			
				125°C	3	12.9	4	15			
r _i	Input resistance			25°C	10 ¹²		10 ¹²		Ω		
c _i	Input capacitance			25°C	5		4		pF		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω		25°C	70	87	75	94	dB		
				-55°C	70	87	70	94			
				125°C	70	87	70	94			
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} /ΔV _{IO})	V _O = 0, R _S = 50 Ω		25°C	75	96	75	96	dB		
				-55°C	75	95	75	95			
				125°C	75	96	75	96			

† Full range is -55°C to 125°C.

‡ Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

§ At V_{CC±} = ±5 V, V_O = ±2.3 V; at V_{CC±} = ±15 V, V_O = ±10 V.



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TL034M and TL034AM electrical characteristics at specified free-air temperature (continued)

PARAMETER	TEST CONDITIONS	T _A	TL034M, TL034AM						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
P _D Total power dissipation (two amplifiers)	V _O = 0, No load	25°C	7.7 10			26 34			mW
		–55°C	4.6 12			18.7 45			
		125°C	7.1 12			23.6 45			
I _{CC} Supply current (two amplifiers)	V _O = 0, No load	25°C	0.77 1			0.87 1.12			mA
		–55°C	0.46 1.2			0.62 1.5			
		125°C	0.71 1.2			0.79 1.5			
V _{O1} /V _{O2} Crosstalk attenuation	A _{VD} = 100	25°C	120			120			dB

TL034M and TL034AM operating characteristics at specified free-air temperature

PARAMETER		TEST CONDITIONS		T _A	TL034M, TL034AM						UNIT
					V _{CC±} = ±5 V			V _{CC±} = ±15 V			
					MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain†	R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	2			1.5	2.9		V/μs	
			–55°C	1.4			1	1.9			
			125°C	2.4			1	3.5			
SR–	Negative slew rate at unity gain†		25°C	3.9			1.5	5.1		V/μs	
			–55°C	3.2			1	4.6			
			125°C	4.1			1	4.7			
t _r	Rise time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	138			132			ns	
			–55°C	142			123				
			125°C	166			58				
t _f	Fall time	V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figure 1	25°C	138			132			ns	
			–55°C	142			123				
			125°C	166			158				
Overshoot factor		V _{I(PP)} = ±10 V, R _L = 10 kΩ, C _L = 100 pF, See Figures 1 and 2	25°C	11%			5%				
			–55°C	16%			6%				
			125°C	14%			8%				
V _n	Equivalent input noise voltage	TL034M	f = 10 Hz	25°C	83			83			nV/√Hz
			f = 1 kHz		43			43			
		TL034AM	f = 10 Hz	25°C	83			83			
			f = 1 kHz		43			43			
I _n	Equivalent input noise current	f = 1 kHz		25°C	0.003			0.003			pA/√Hz
B1	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4	25°C	1			1.1			MHz	
			–55°C	1			1.1				
			125°C	0.9			0.9				
ϕ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF, R _L = 10 kΩ, See Figure 4	25°C	61°			65°				
			–55°C	57°			64°				
			125°C	59°			62°				

[†] For V_{CC±} = ±5 V, V_I(PP) = ±1 V; for V_{CC±} = ±15 V, V_I(PP) = ±5 V.

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TL034Y electrical characteristics, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	TL034Y						UNIT
			V _{CC±} = ±5 V			V _{CC±} = ±15 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	V _O = 0, V _{IC} = 0, R _S = 50 Ω	0.91			0.79			mV
α _{VIO}	Temperature coefficient of input offset voltage		11.6			12			μV/°C
I _{IO}	Input offset current	V _O = 0, V _{IC} = 0, See Figure 5	1			1			pA
			2			2			
I _{IB}	Input bias current	V _O = 0, V _{IC} = 0, See Figure 5	2			2			pA
			7			8			nA
V _{ICR}	Common-mode input voltage range		−3.4 to 5.4			−13.4 to 15.4			V
V _{OM+}	Maximum positive peak output voltage swing	R _L = 10 kΩ	4.3			14			V
V _{OM−}	Maximum negative peak output voltage swing	R _L = 10 kΩ	−4.2			−13.9			V
A _{VD}	Large-signal differential voltage amplification†	R _L = 10 kΩ	12			14.3			V/mV
r _i	Input resistance		10 ¹²			10 ¹²			Ω
c _i	Input capacitance		5			4			pF
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICRmin} , V _O = 0, R _S = 50 Ω	87			94			dB
k _{SVR}	Supply-voltage rejection ratio (ΔV _{CC±} / ΔV _{IO})	V _O = 0, R _S = 50 Ω	96			96			dB
P _D	Total power dissipation (four amplifiers)	V _O = 0, No load	7.7			26			mW
I _{CC}	Supply current (four amplifiers)	V _O = 0, No load	0.77			0.87			mA
V _{O1} /V _{O2}	Crosstalk attenuation	A _{VD} = 100	120			120			dB

† At $V_{CC\pm} = \pm 5\text{ V}$, $V_O = \pm 2.3\text{ V}$; at $V_{CC\pm} = \pm 15\text{ V}$, $V_O = \pm 10\text{ V}$.

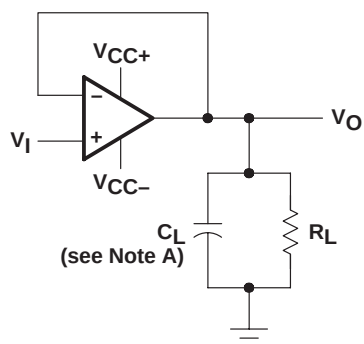
TL034Y operating characteristics, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		TL034Y						UNIT
				V _{CC±} = ±5 V			V _{CC±} = ±15 V			
				MIN	TYP	MAX	MIN	TYP	MAX	
SR+	Positive slew rate at unity gain	R _L = 10 kΩ, C _L = 100 pF, See Figure 1	2			1.5	2.9		V/μs	
SR−	Negative slew rate at unity gain		3.9			1.5	5.1		V/μs	
t _r	Rise time	V _{I(PP)} = ±10 V,		138			132		ns	
t _f	Fall time	R _L = 10 kΩ, C _L = 100 pF,		138			132		ns	
Overshoot factor		See Figures 1 and 2		11%			5%			
V _n	Equivalent input noise voltage	R _S = 20 Ω, See Figure 3	f = 10 kHz	83			83		nV/√Hz	
			f = 1 kHz	43			43			
I _n	Equivalent input noise current	f = 1 kHz		0.003			0.003		pA/√Hz	
B1	Unity-gain bandwidth	V _I = 10 mV, C _L = 25 pF,	R _L = 10 kΩ, See Figure 4	1			1.1		MHz	
φ _m	Phase margin at unity gain	V _I = 10 mV, C _L = 25 pF,	R _L = 10 kΩ, See Figure 4	61°			65°			

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PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes fixture capacitance.

Figure 1. Slew-Rate and Overshoot Test Circuit

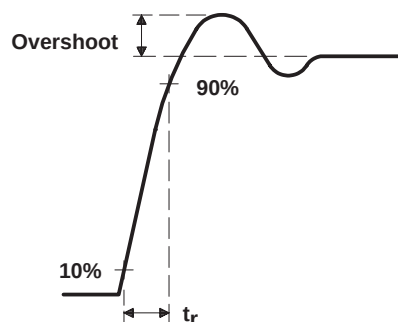


Figure 2. Rise Time and Overshoot Waveform

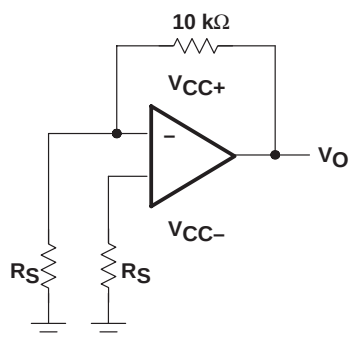
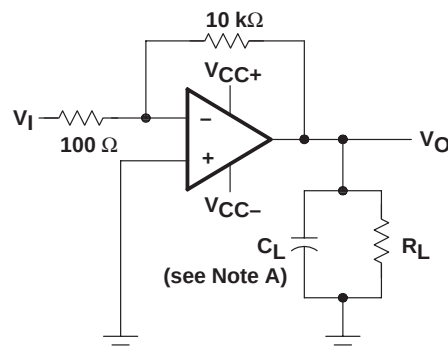


Figure 3. Noise-Voltage Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 4. Unity-Gain Bandwidth and Phase-Margin Test Circuit

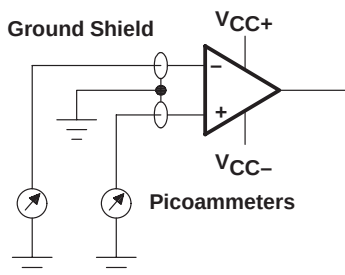


Figure 5. Input-Bias and Offset-Current Test Circuit

PARAMETER MEASUREMENT INFORMATION

typical values

Typical values presented in this data sheet represent the median (50% point) of device parametric performance.

input bias and offset current

At the picoampere bias current level typical of the TL03x and TL03xA, accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test-socket leakages easily can exceed the actual device bias currents. To accurately measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied but with no device in the socket. The device is then inserted into the socket and a second test that measures both the socket leakage and the device input bias current is performed. The two measurements are then subtracted algebraically to determine the bias current of the device.

noise

With the increasing emphasis on low noise levels in many of today's applications, the input noise voltage density is performed at $f = 1$ kHz, unless otherwise noted.

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TYPICAL CHARACTERISTICS

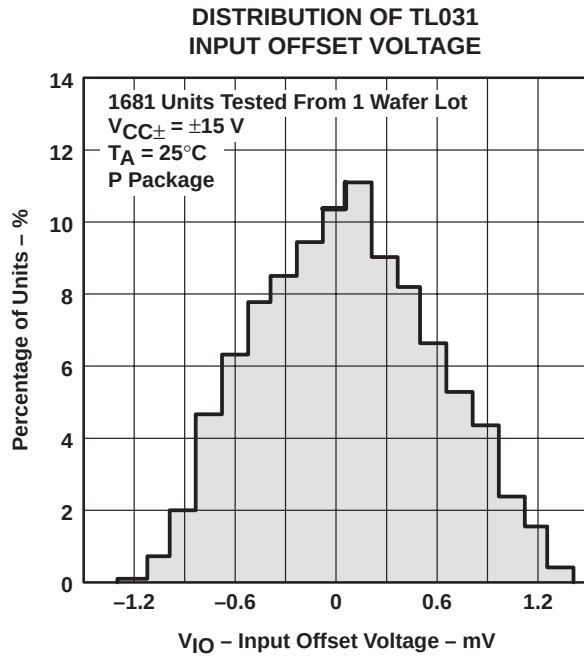


Figure 6

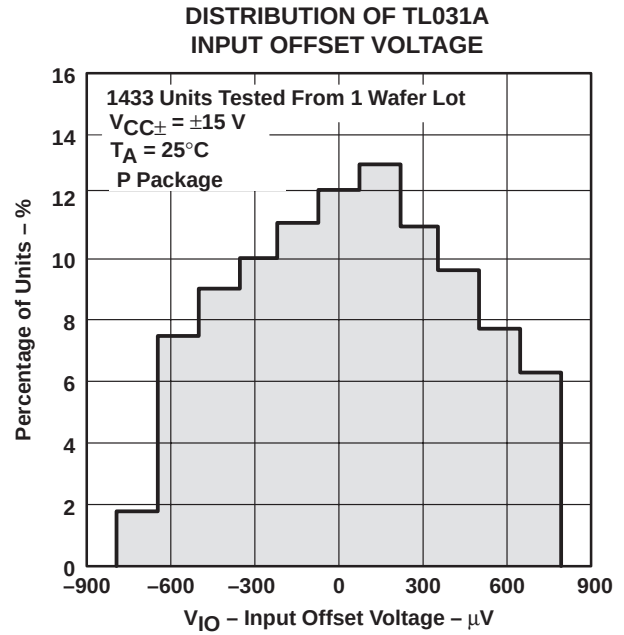


Figure 7

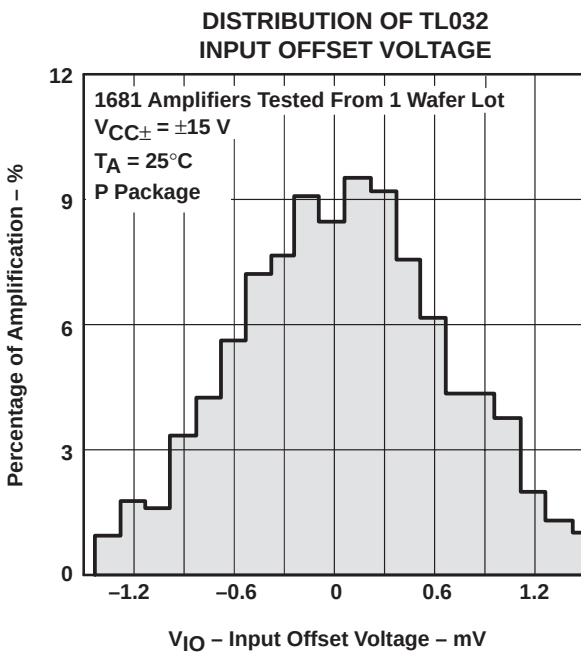


Figure 8

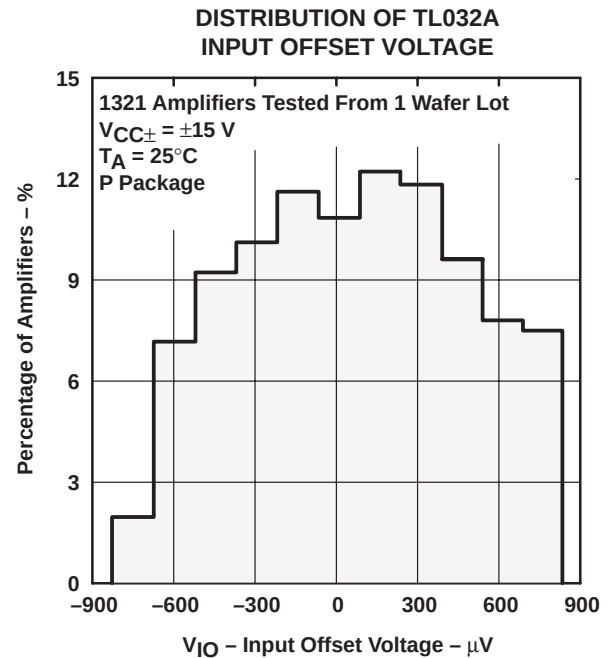


Figure 9

TL03x, TL03xA, TL03xY

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**DISTRIBUTION OF TL034
INPUT OFFSET VOLTAGE**

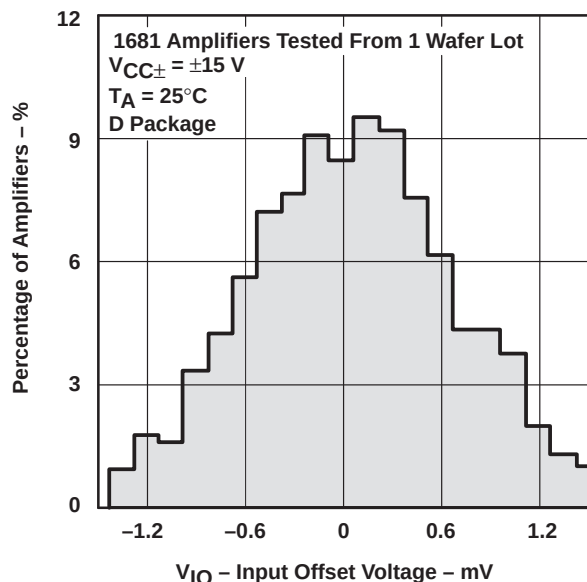


Figure 10

**DISTRIBUTION OF TL034A
INPUT OFFSET VOLTAGE**

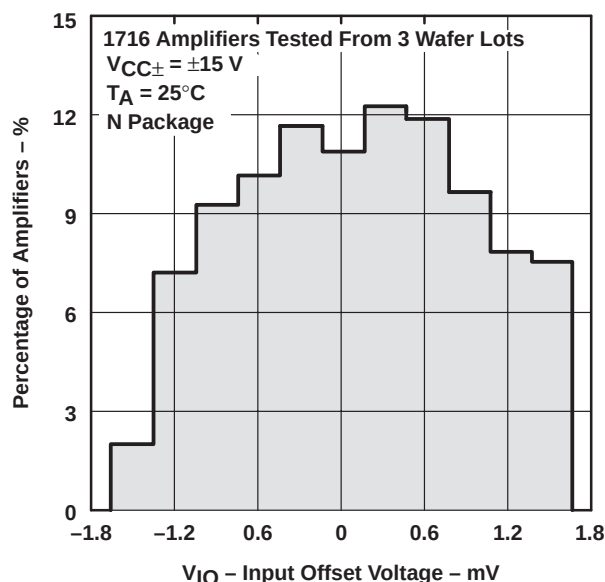


Figure 11

**DISTRIBUTION OF TL031
INPUT OFFSET-VOLTAGE
TEMPERATURE COEFFICIENT**

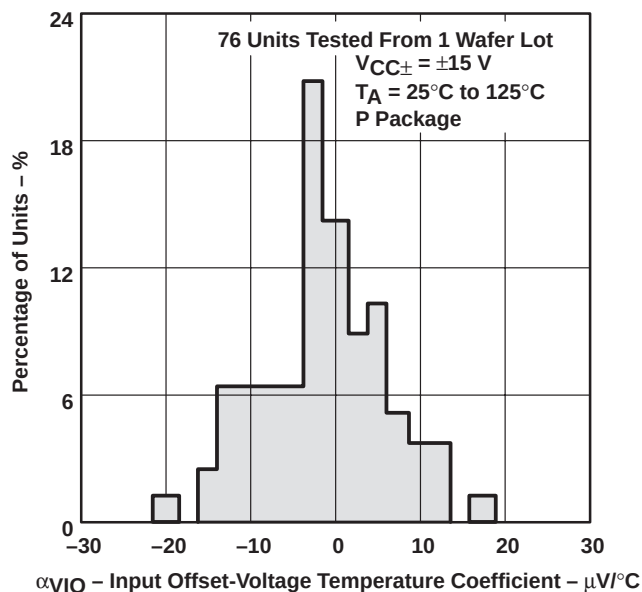


Figure 12

**DISTRIBUTION OF TL032
INPUT OFFSET-VOLTAGE
TEMPERATURE COEFFICIENT**

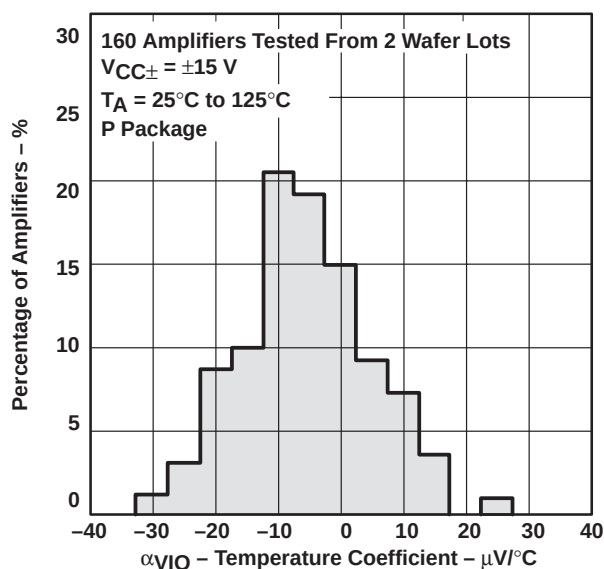


Figure 13

TYPICAL CHARACTERISTICS

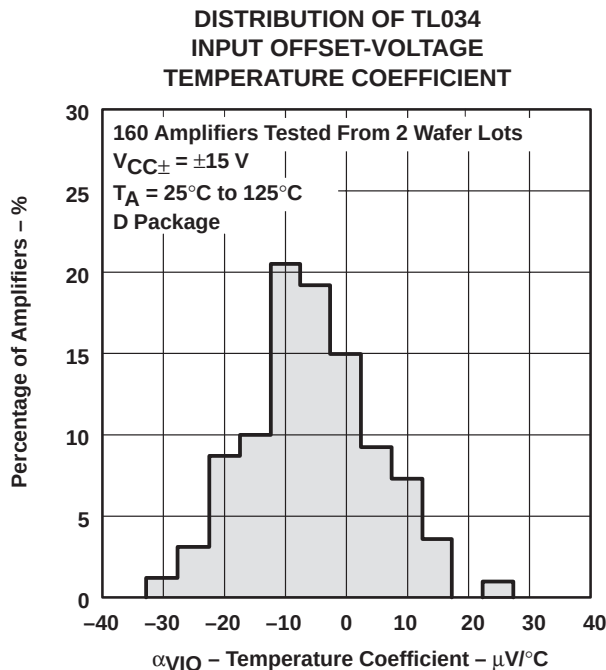


Figure 14

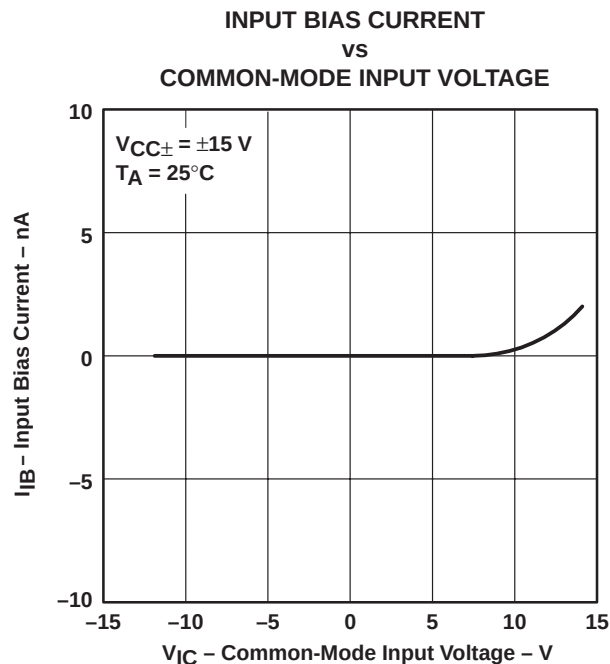


Figure 15

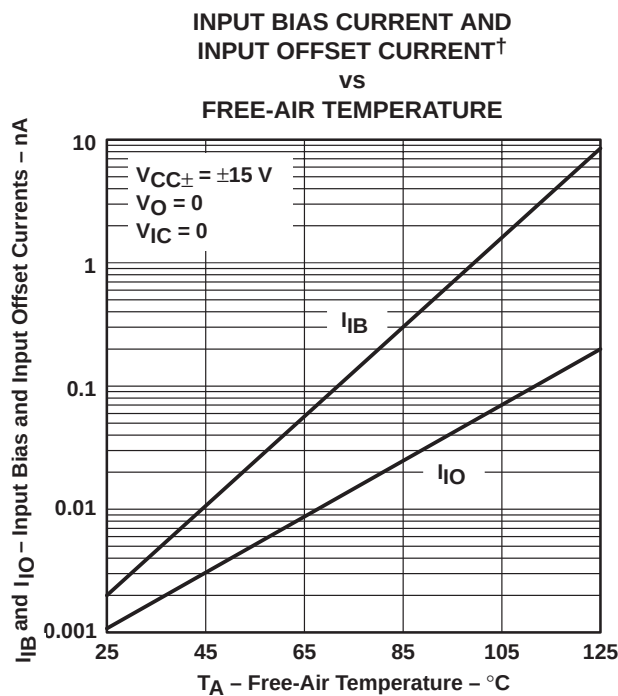


Figure 16

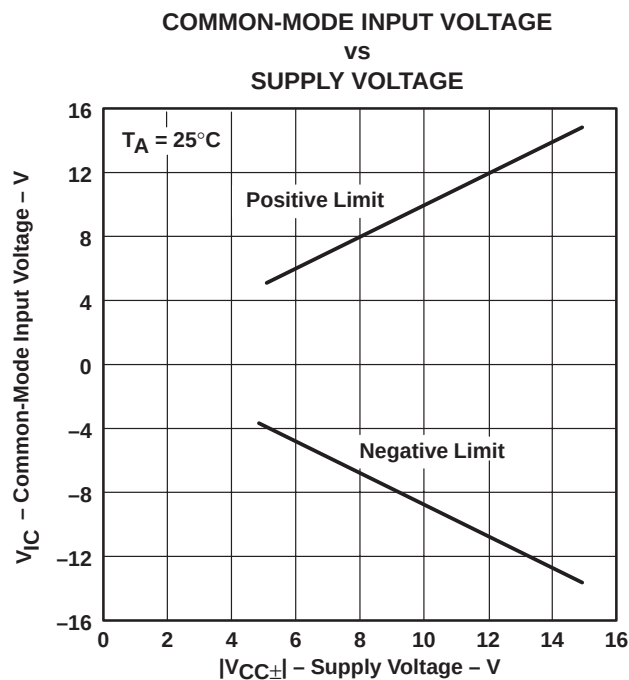


Figure 17

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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COMMON-MODE INPUT VOLTAGE RANGE†
VS
FREE-AIR TEMPERATURE

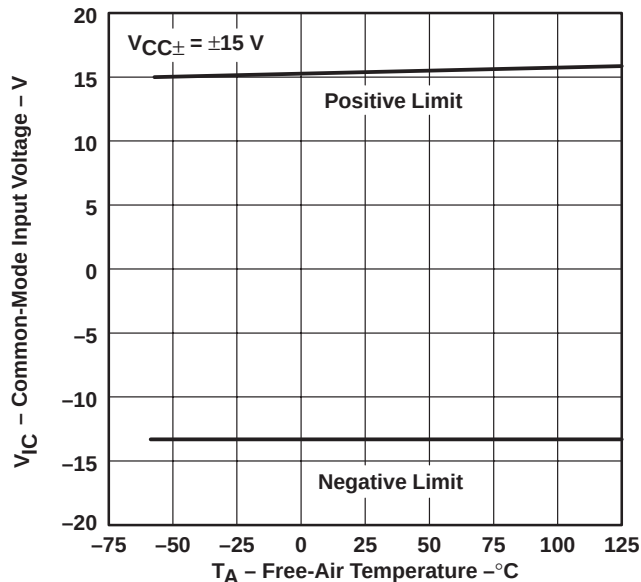


Figure 18

OUTPUT VOLTAGE
VS
DIFFERENTIAL INPUT VOLTAGE

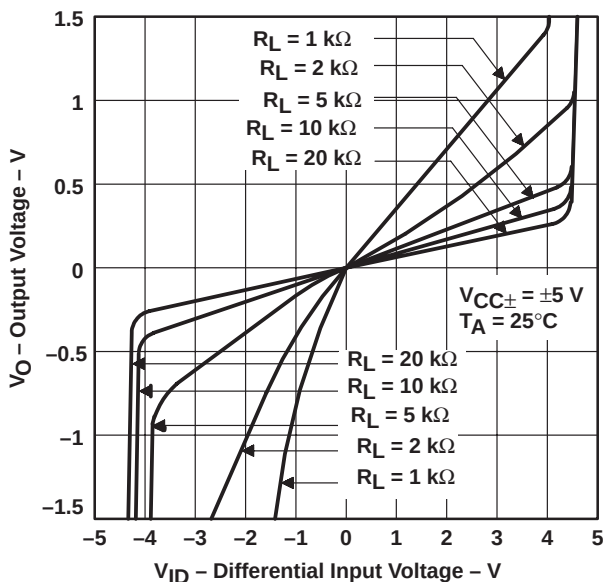


Figure 19

OUTPUT VOLTAGE
VS
DIFFERENTIAL INPUT VOLTAGE

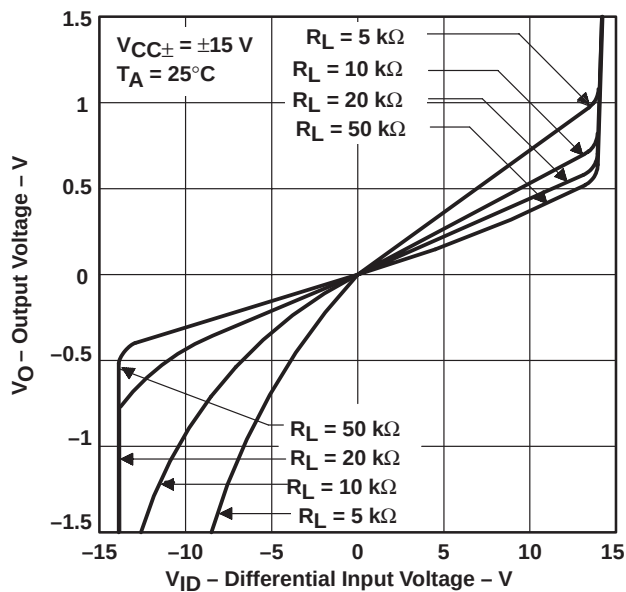


Figure 20

MAXIMUM PEAK OUTPUT VOLTAGE
VS
SUPPLY VOLTAGE

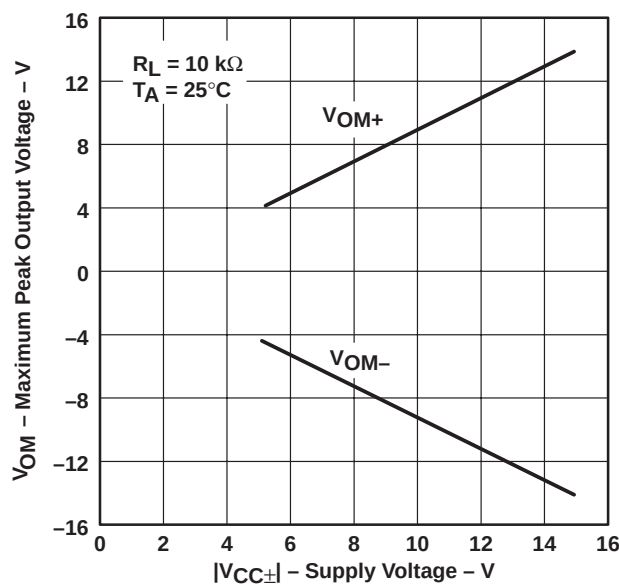


Figure 21

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

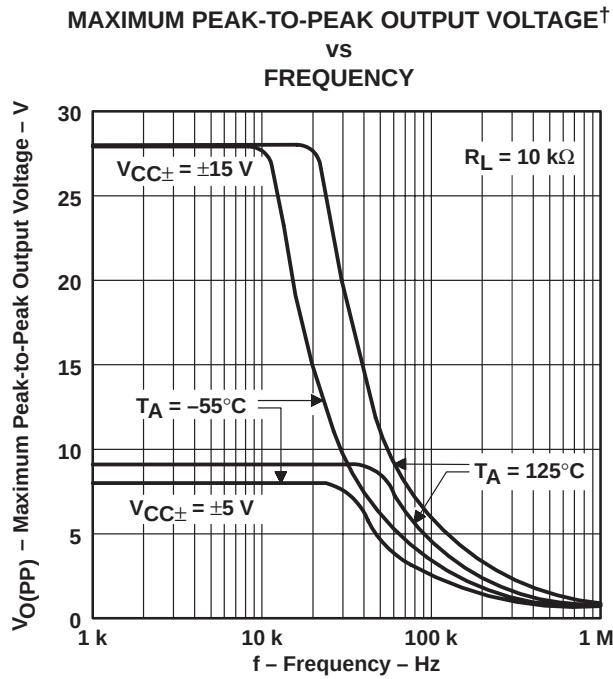


Figure 22

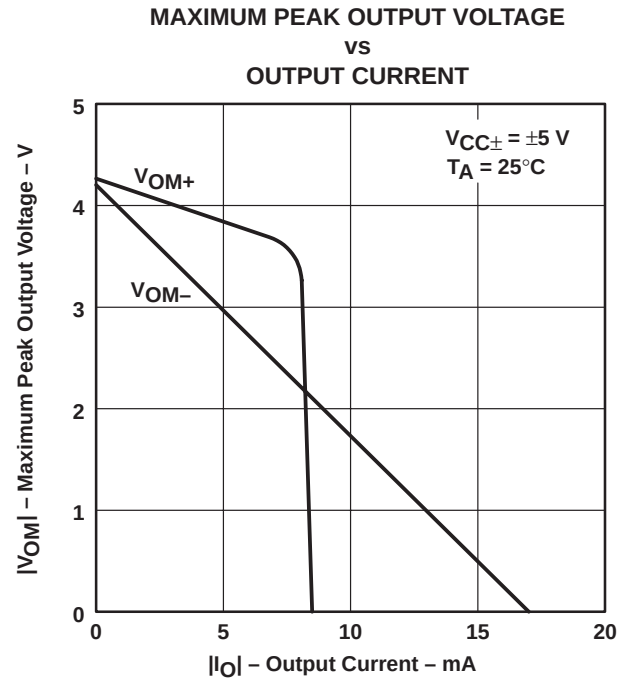


Figure 23

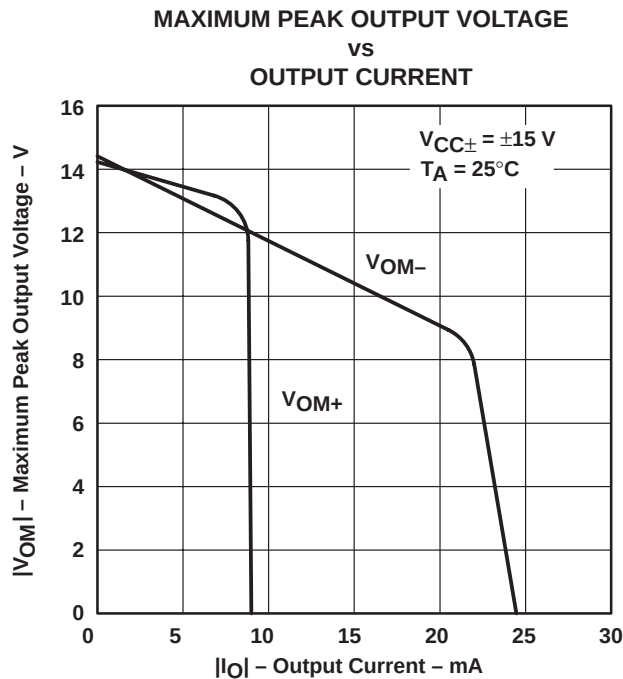


Figure 24

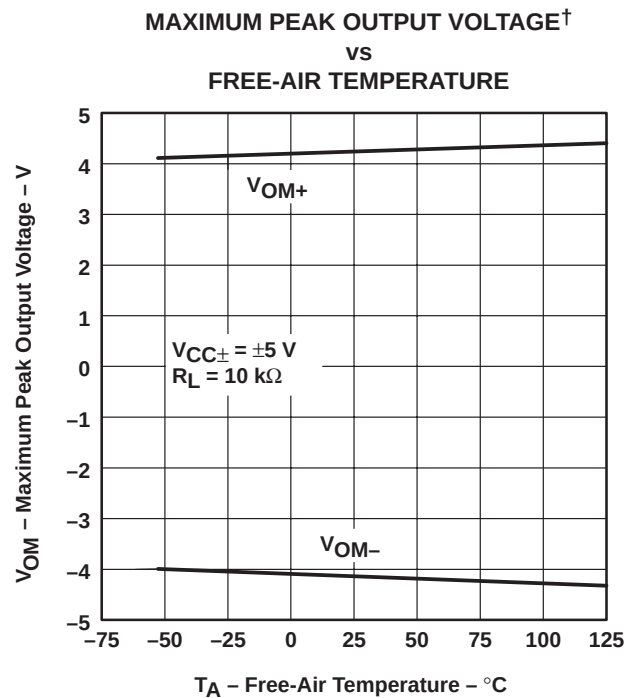


Figure 25

[†] Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

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TYPICAL CHARACTERISTICS

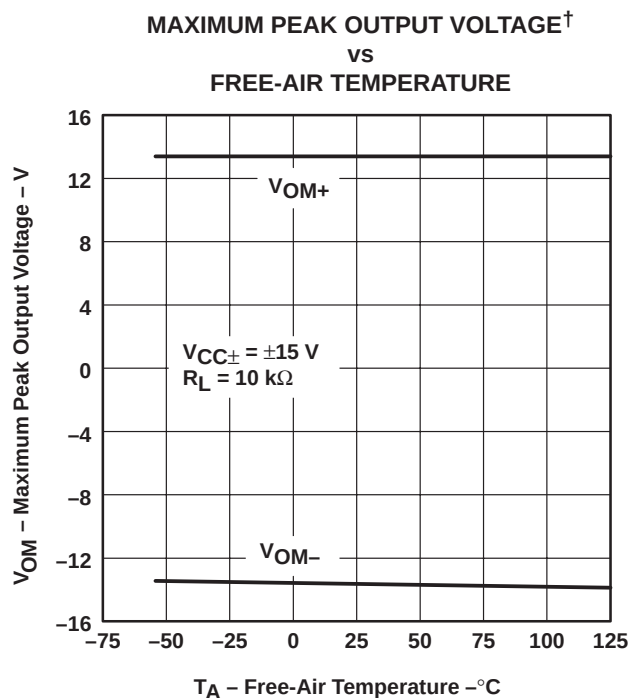


Figure 26

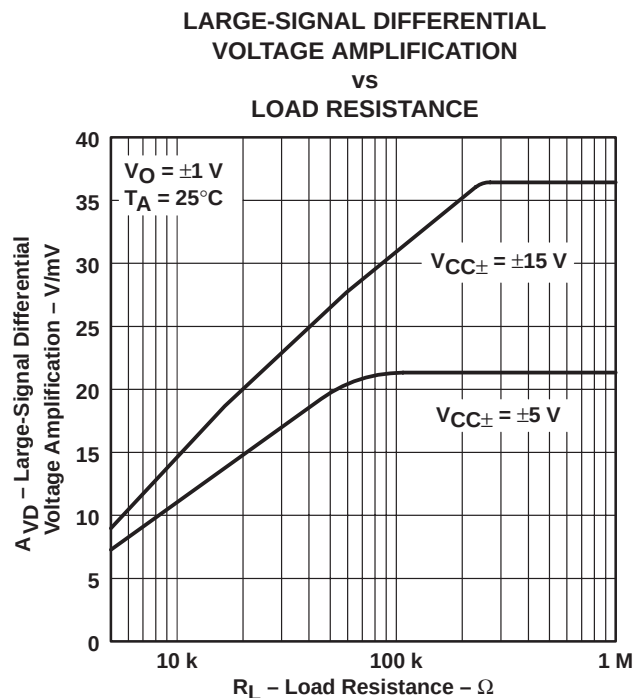


Figure 27

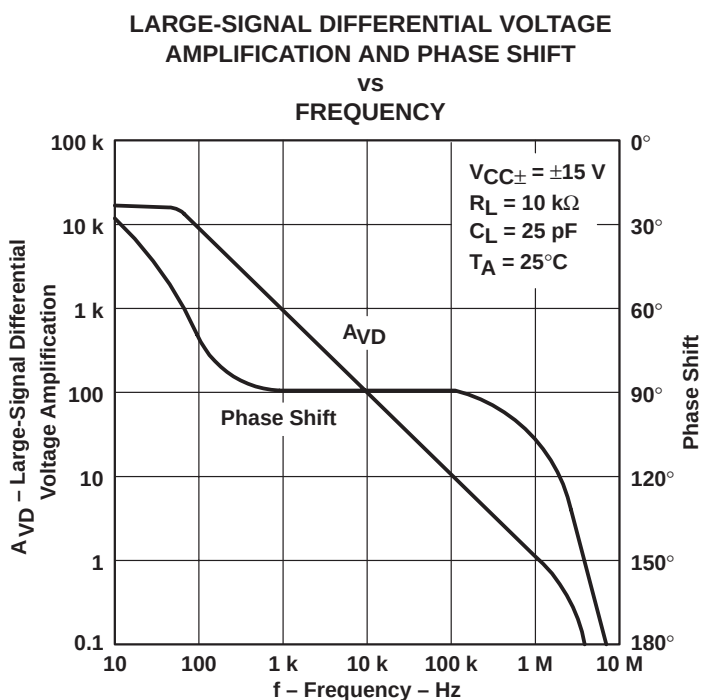


Figure 28

[†] Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

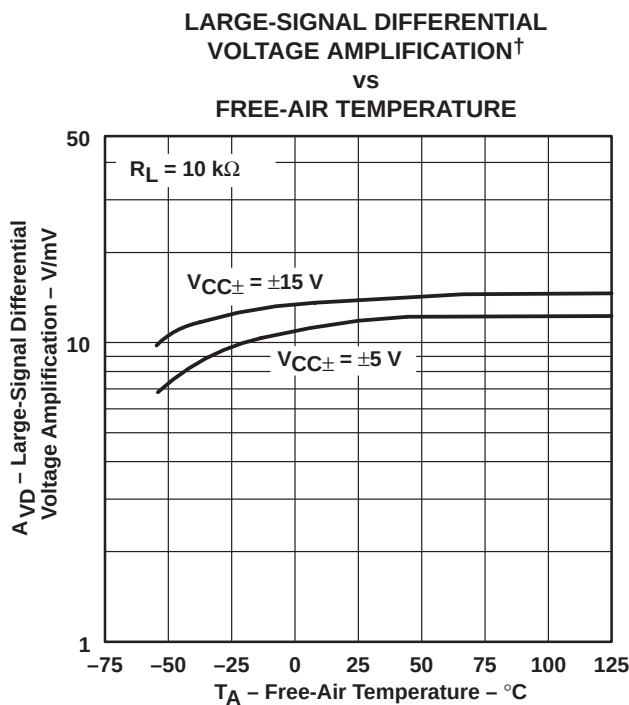


Figure 29

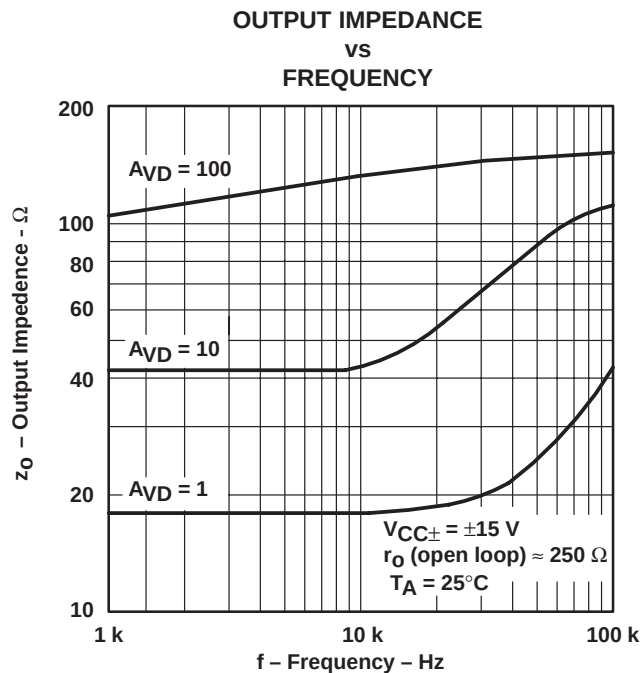


Figure 30

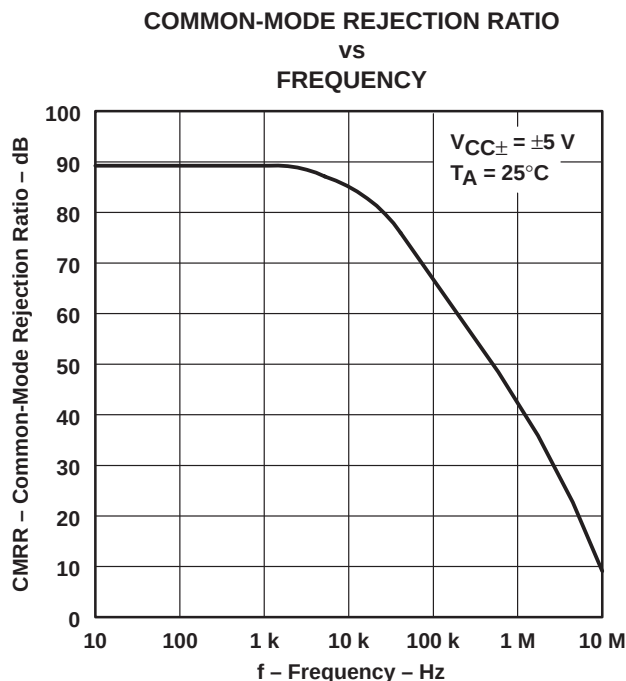


Figure 31

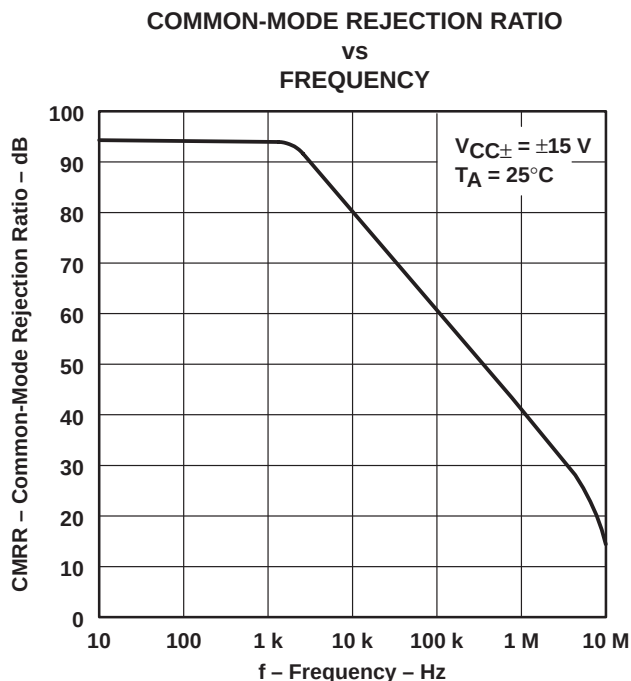


Figure 32

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TL03x, TL03xA, TL03xY

ENHANCED-JFET LOW-POWER LOW-OFFSET

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TYPICAL CHARACTERISTICS

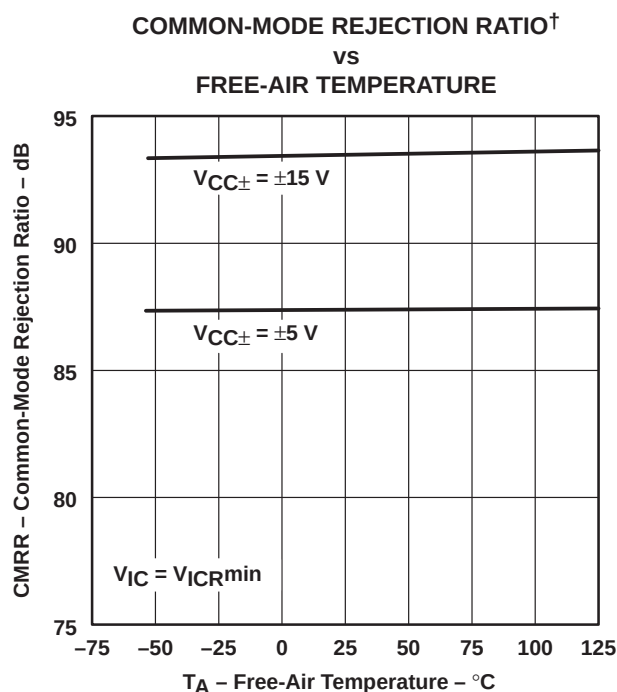


Figure 33

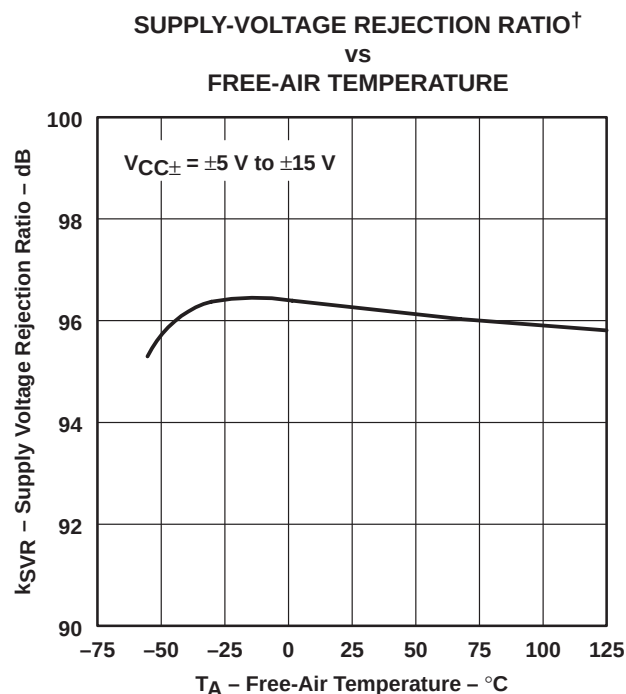


Figure 34

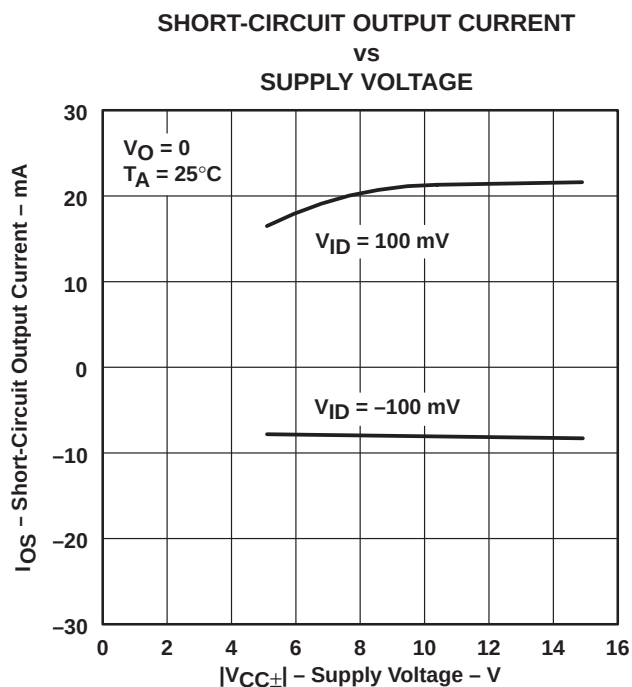


Figure 35

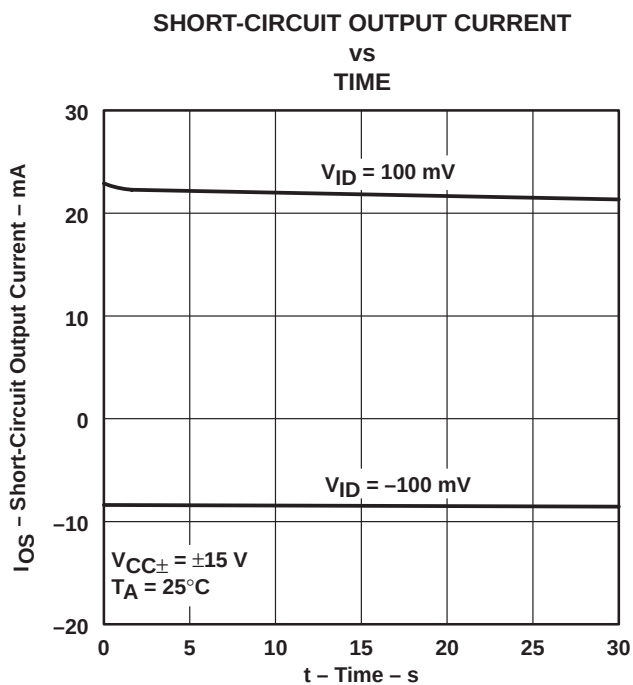


Figure 36

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

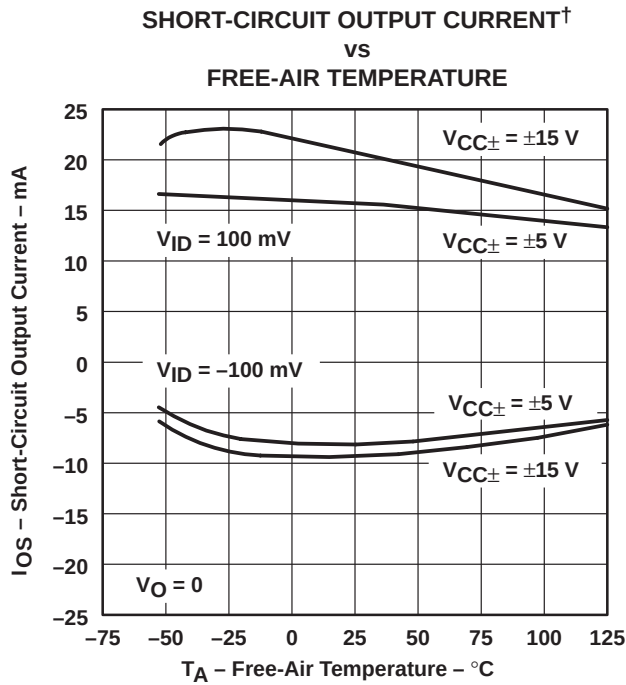


Figure 37

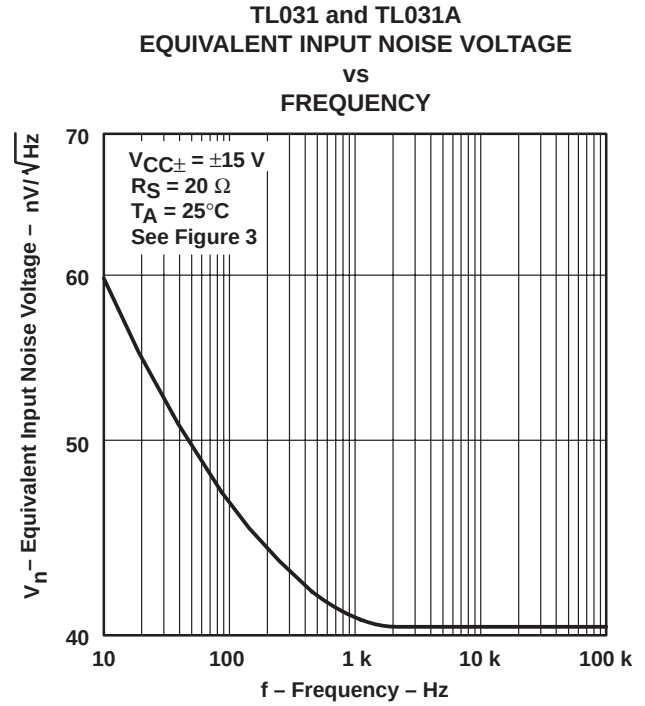


Figure 38

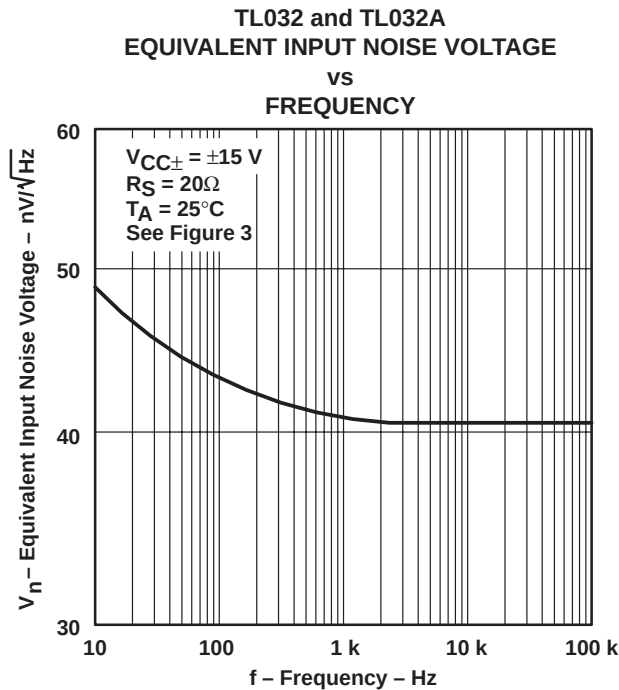


Figure 39

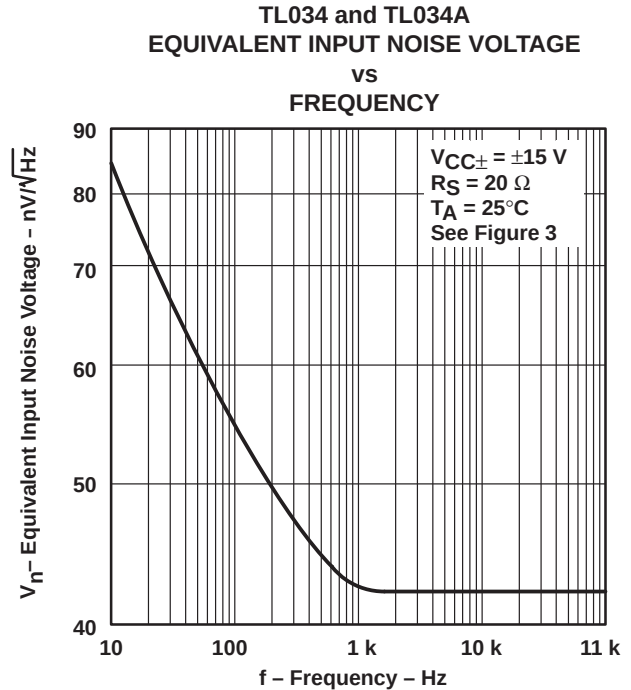


Figure 40

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TL03x, TL03xA, TL03xY

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TYPICAL CHARACTERISTICS

TL031 and TL031A
SUPPLY CURRENT[†]
vs
SUPPLY VOLTAGE

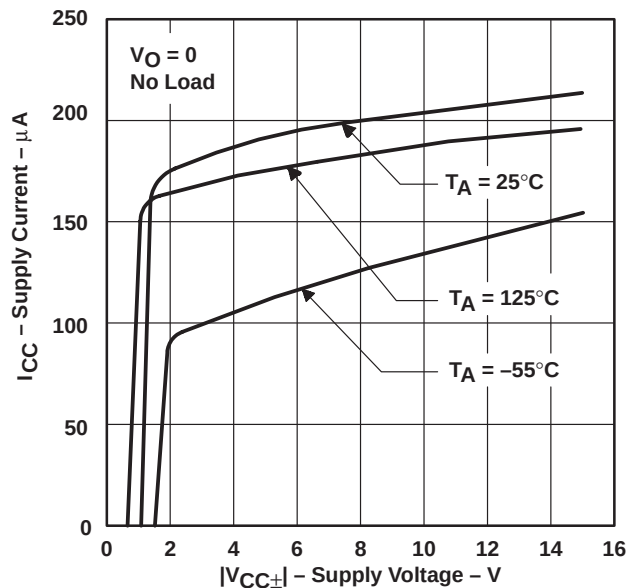


Figure 41

TL032 and TL032A
SUPPLY CURRENT[†]
vs
SUPPLY VOLTAGE

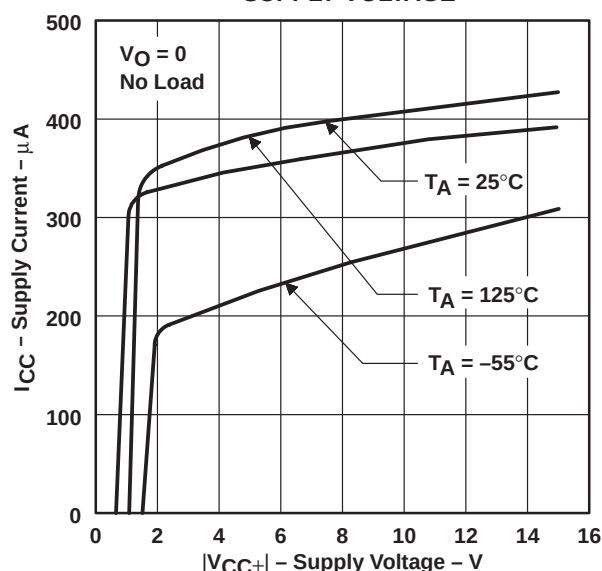


Figure 42

TL034 and TL034A
SUPPLY CURRENT[†]
vs
SUPPLY VOLTAGE

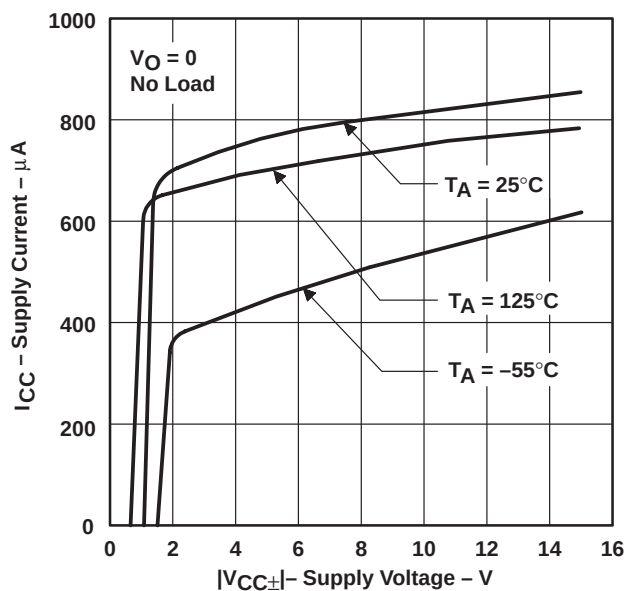


Figure 43

TL031 and TL031A
SUPPLY CURRENT[†]
vs
FREE-AIR TEMPERATURE

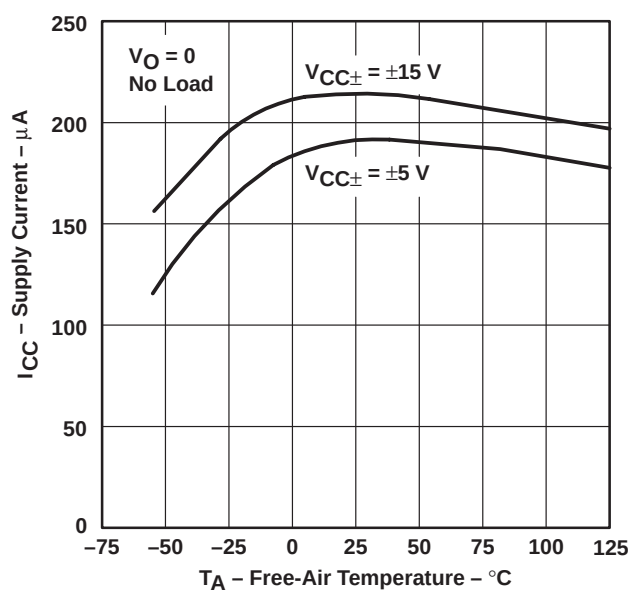


Figure 44

[†] Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

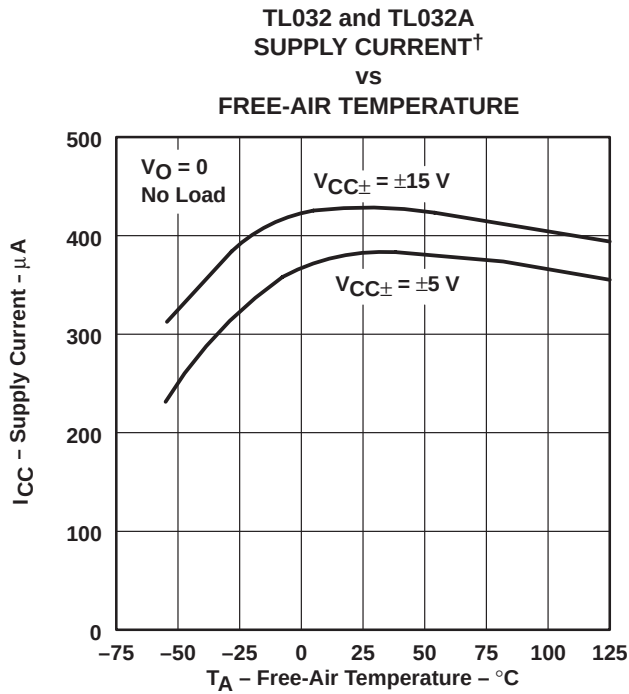


Figure 45

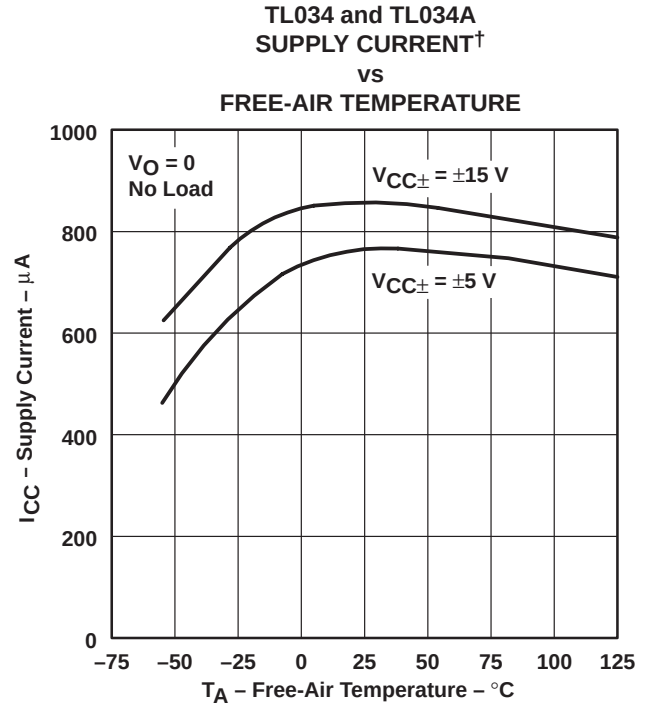


Figure 46

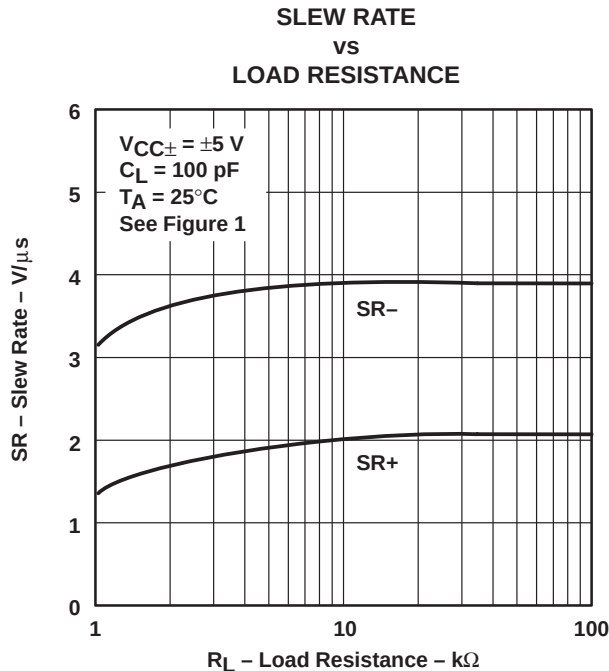


Figure 47

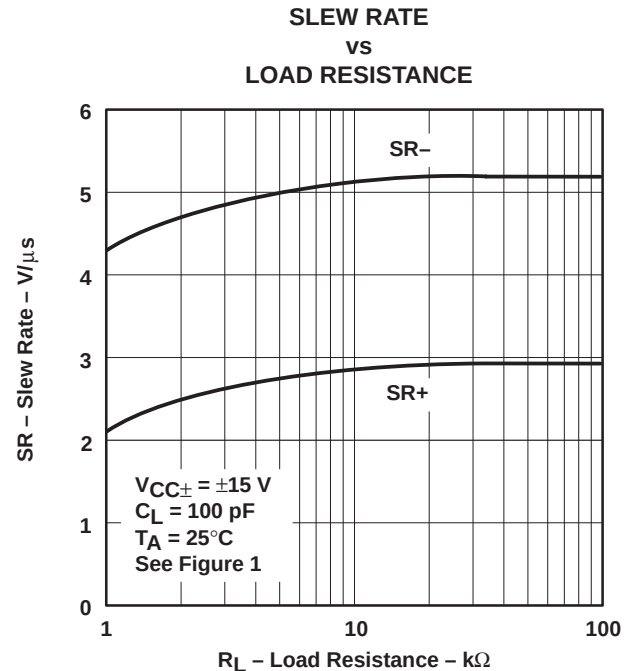


Figure 48

† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TL03x, TL03xA, TL03xY

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TYPICAL CHARACTERISTICS

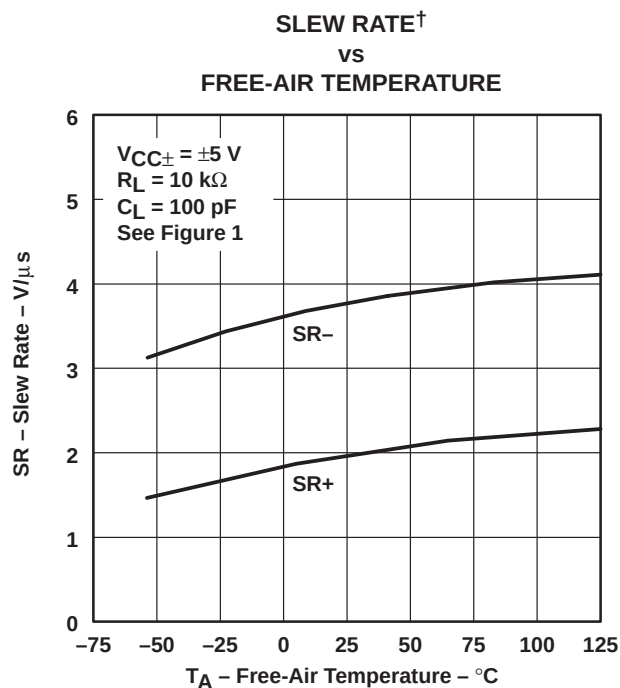


Figure 49

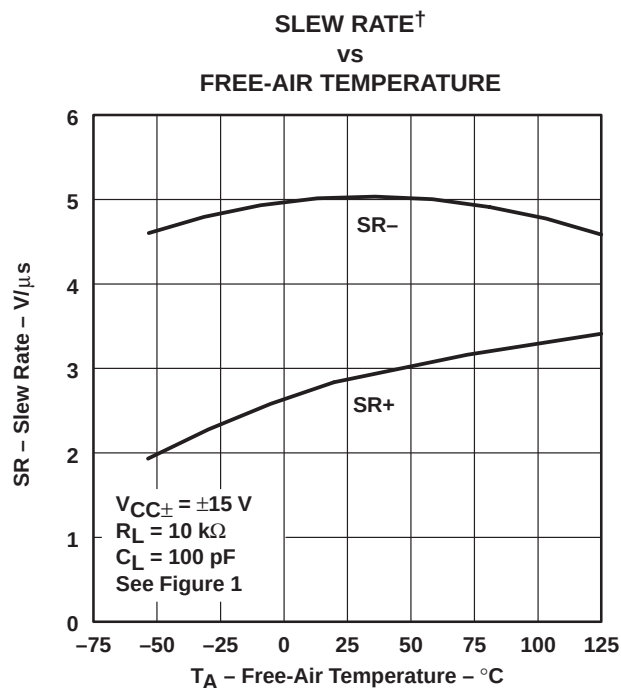


Figure 50

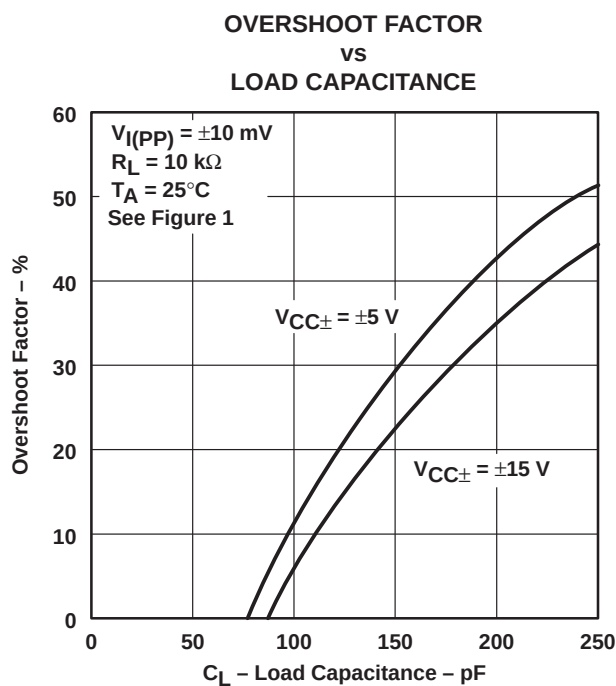


Figure 51

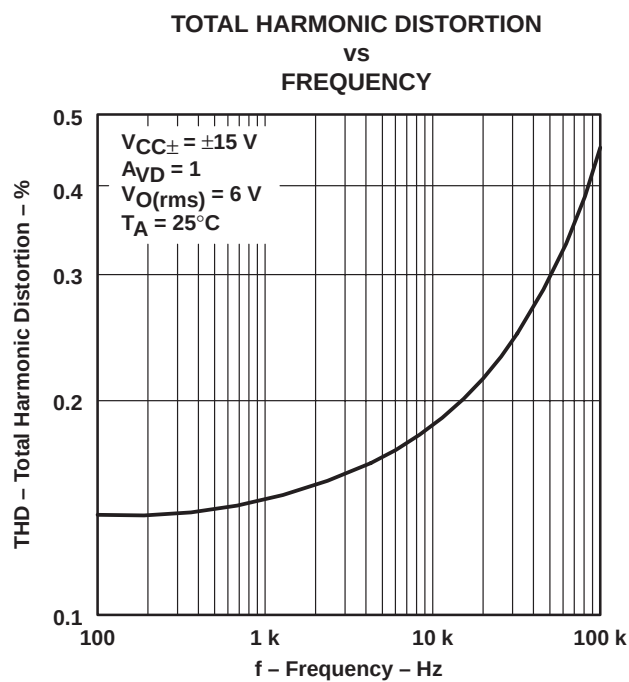


Figure 52

[†] Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

TL03x, TL03xA, TL03xY ENHANCED-JFET LOW-POWER LOW-OFFSET OPERATIONAL AMPLIFIERS

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TYPICAL CHARACTERISTICS

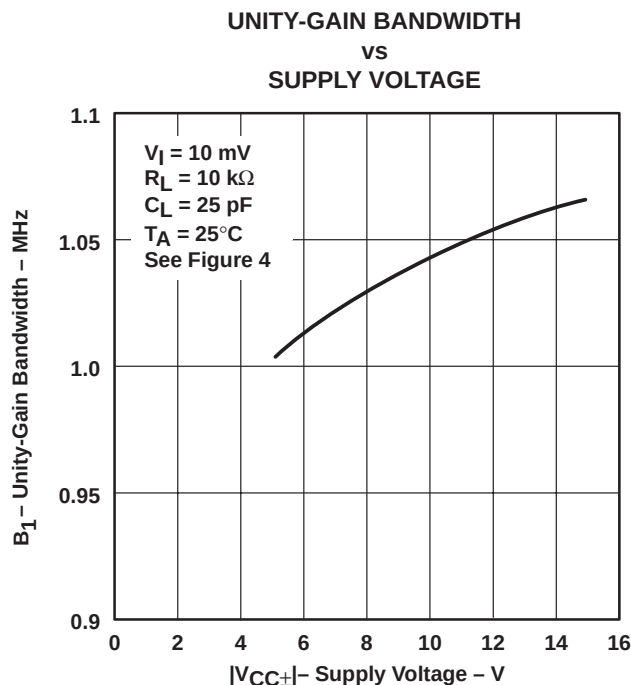


Figure 53

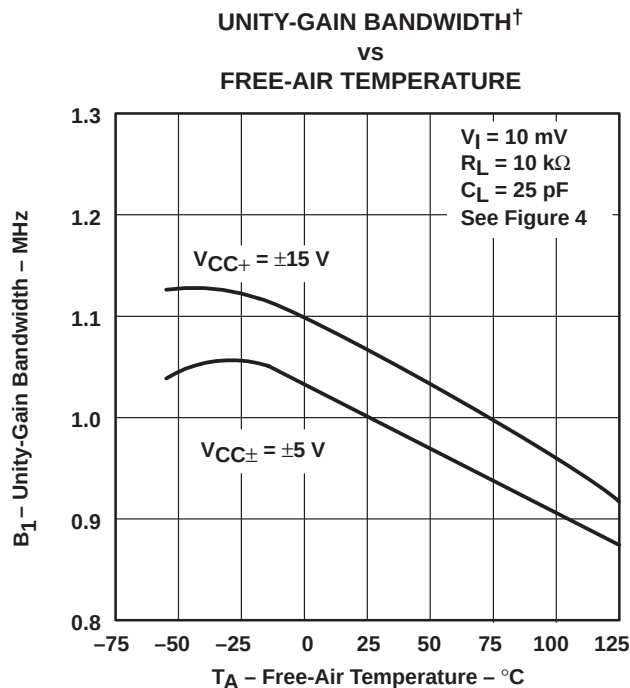


Figure 54

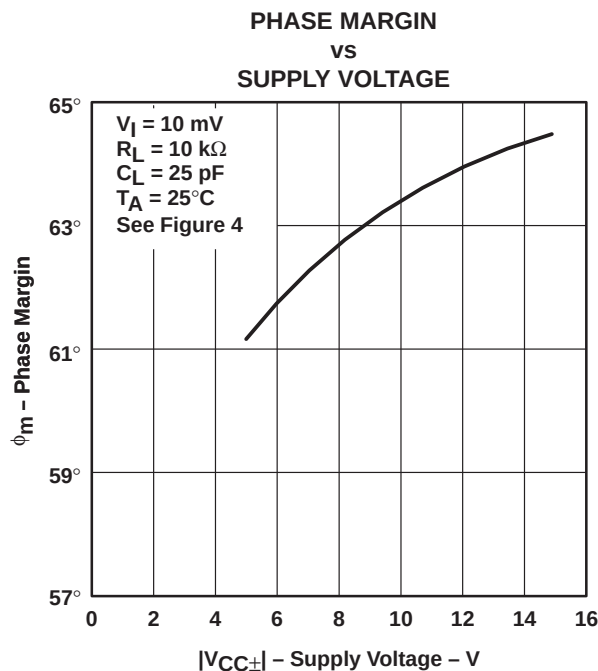
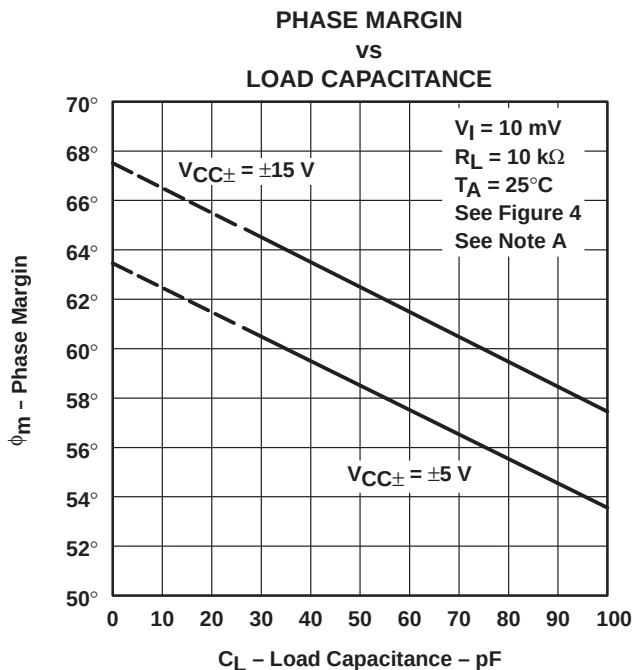


Figure 55



NOTE A: Values of phase margin below a load capacitance of 25 pF were estimated.

Figure 56

[†] Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

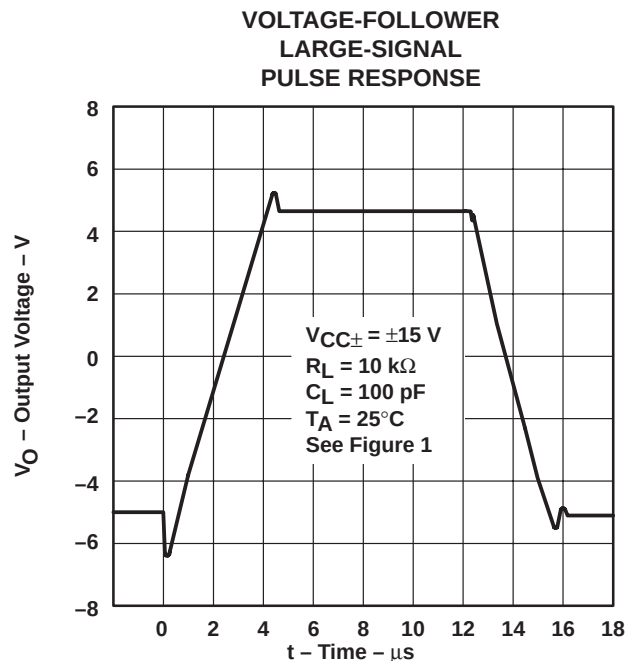
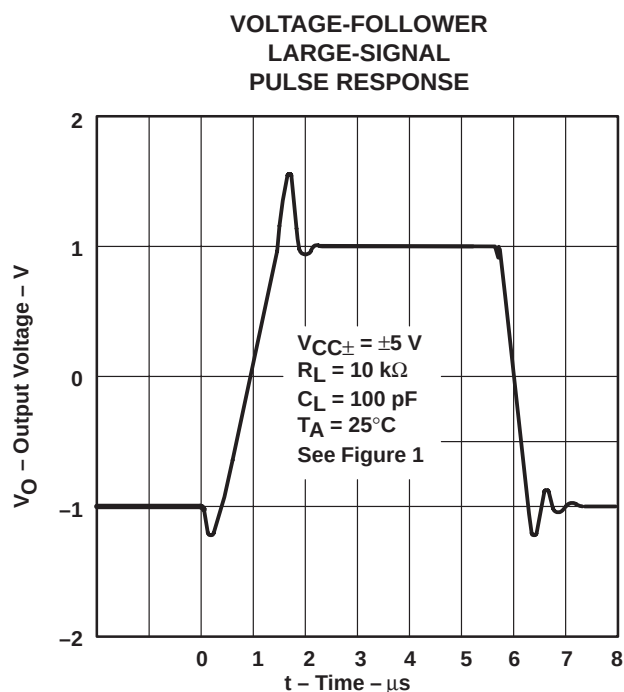
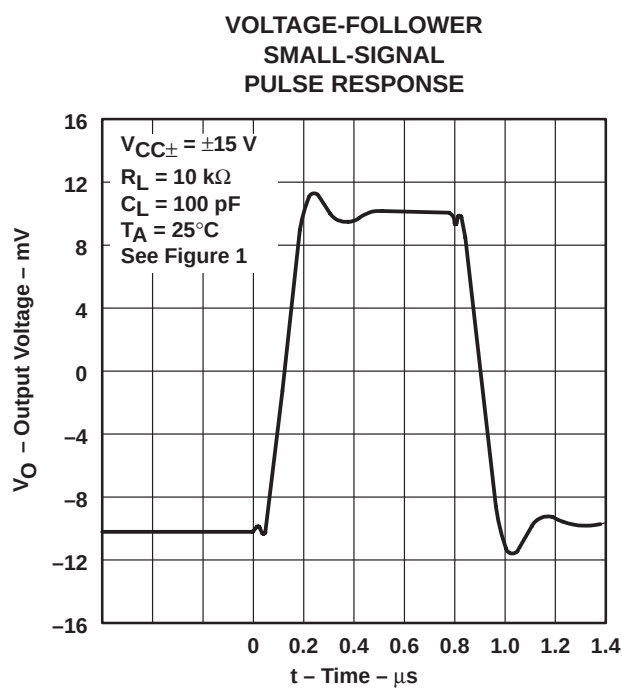
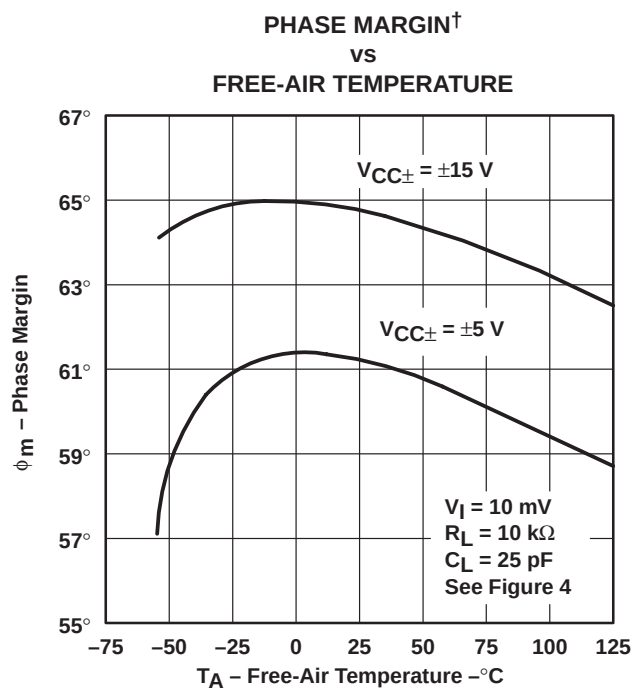
TL03x, TL03xA, TL03xY

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TYPICAL CHARACTERISTICS



† Data at high and low temperatures are applicable only within the recommended operating free-air temperature ranges of the various devices.

APPLICATION INFORMATION

input characteristics

The TL03x and TL03xA are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction.

Due to the extremely high input impedance and resulting low bias-current requirements, the TL03x and TL03xA are well suited for low-level signal processing; however, leakage currents on printed circuit boards and sockets easily can exceed bias current requirements and cause degradation in system performance. It is a good practice to include guard rings around inputs (see Figure 61). These guard rings should be driven from a low-impedance source at the same voltage level as the common-mode input.

Unused amplifiers should be connected as grounded unity-gain followers to avoid oscillation.

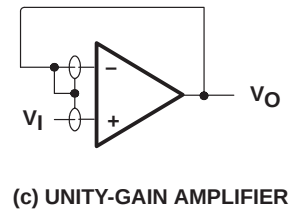
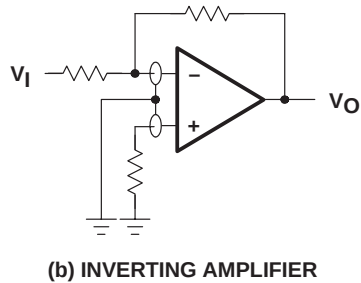
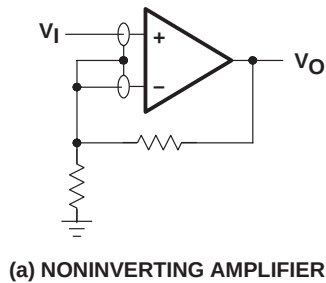


Figure 61. Use of Guard Rings

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APPLICATION INFORMATION

output characteristics

All operating characteristics (except bandwidth and phase margin) are specified with 100-pF load capacitance. The TL03x and TL03xA drive higher capacitive loads; however, as the load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation. The value of the load capacitance at which oscillation occurs varies with production lots. If an application appears to be sensitive to oscillation due to load capacitance, adding a small resistance in series with the load should alleviate the problem (see Figure 63). Capacitive loads of 1000 pF and larger can be driven if enough resistance is added in series with the output (see Figure 62).

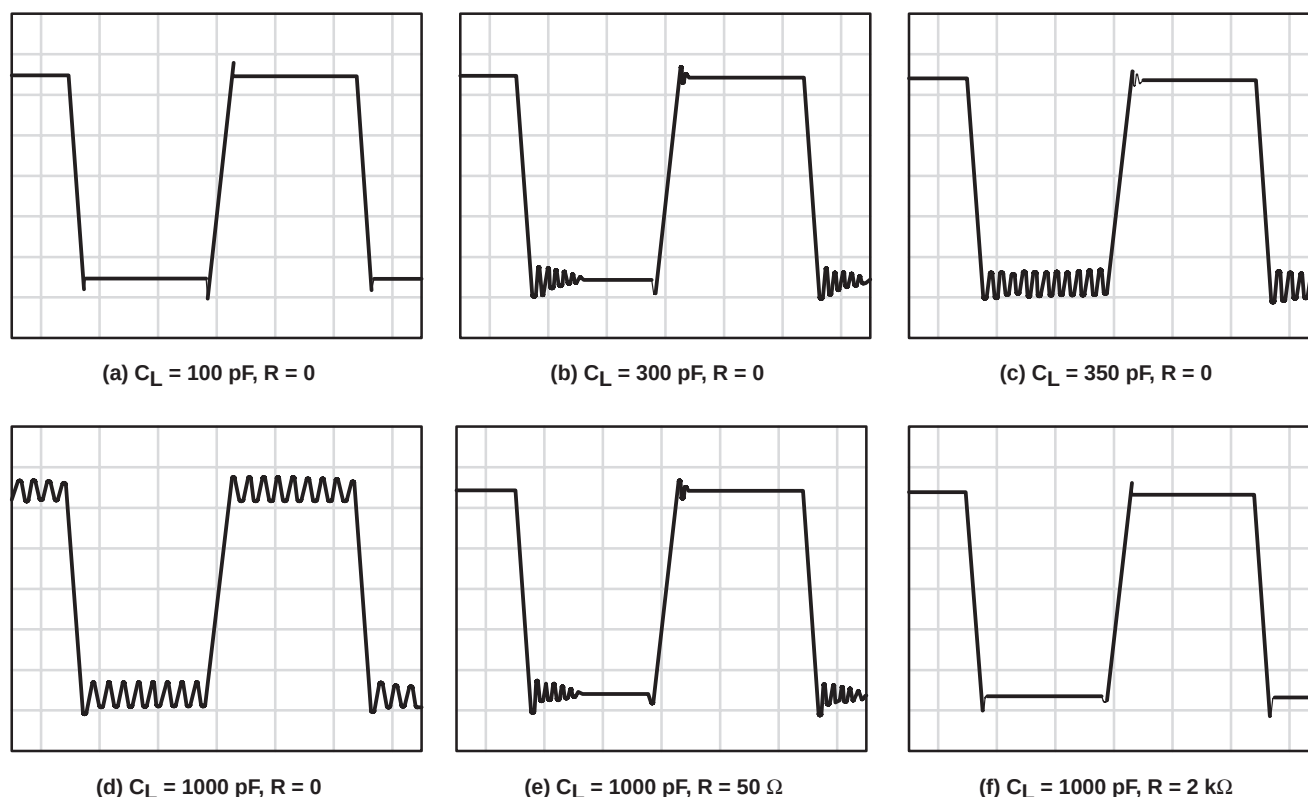


Figure 62. Effect of Capacitive Loads

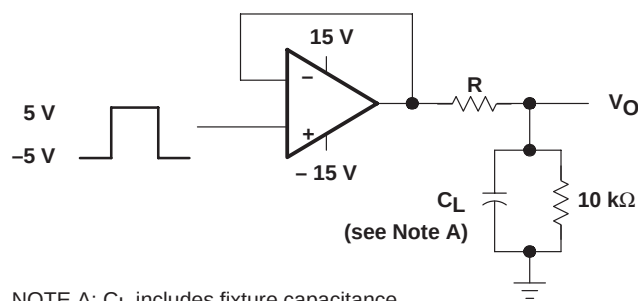


Figure 63. Test Circuit for Output Characteristics

APPLICATION INFORMATION

high-Q notch filter

In general, Texas Instruments enhanced-JFET operational amplifiers serve as excellent filters. The circuit in Figure 64 provides a narrow notch at a specific frequency. Notch filters are designed to eliminate frequencies that are interfering with the operation of an application. For this filter, the center frequency can be calculated as:

$$f_o = \frac{1}{2\pi \times R1 \times C1}$$

With the resistors and capacitors shown in Figure 64, the center frequency is 1 kHz. $C1 = C3 = C2 + 2$ and $R1 = R3 = 2 \times R2$. The center frequency can be modified by varying these values. When adjusting the center frequency, ensure that the operational amplifier has sufficient gain at the frequency required.

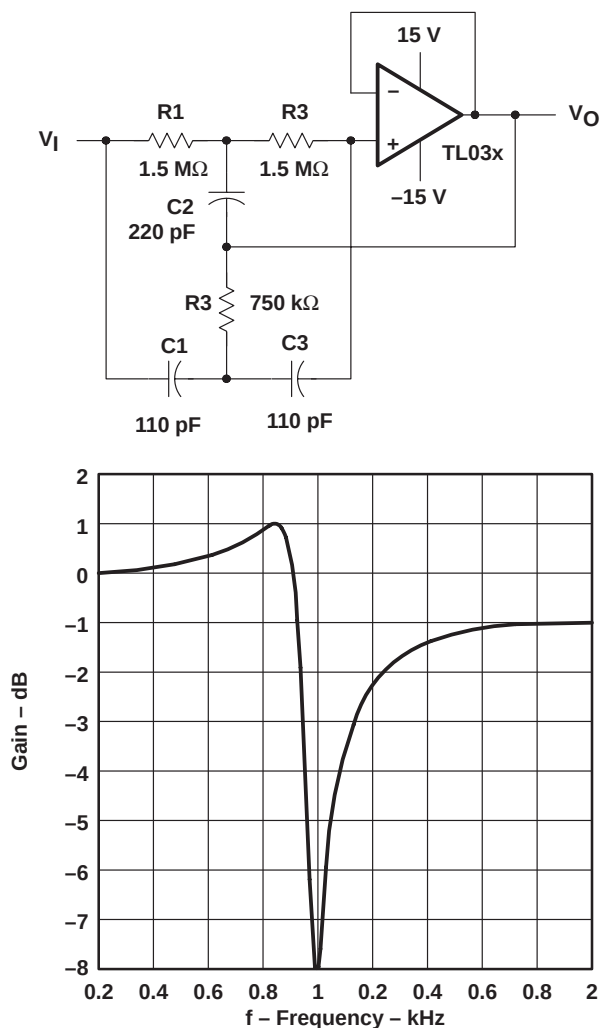


Figure 64. High-Q Notch Filter

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APPLICATION INFORMATION

transimpedance amplifier

The low-power precision TL03x allows accurate measurement of low currents. The high input impedance and low offset voltage of the TL03xA greatly simplify the design of a transimpedance amplifier. At room temperature, this design achieves 10-bit accuracy with an error of less than 1/2 LSB.

Assuming that R_2 is much less than R_1 and ignoring error terms, the output voltage can be expressed as:

$$V_O = -I_{IN} \times R_F \left(\frac{R_1 + R_2}{R_2} \right)$$

Using the resistor values shown in the schematic for a 1-nA input current, the output voltage equals -0.1 V. If the V_O limit for the TL03xA is measured at ± 12 V, the maximum input current for these resistor values is ± 120 nA. Similarly, one LSB on a 10-bit scale corresponds to 12 mV of output voltage, or 120 pA of input current.

The following equation shows the effect of input offset voltage and input bias current on the output voltage:

$$V_O = - \left[V_{IO} + R_F (I_{IO} + I_{IB}) \right] \left(\frac{R_1 + R_2}{R_2} \right)$$

If the application requires input protection for the transimpedance amplifier, do not use standard PN diodes. Instead, use low-leakage Siliconix SN4117 JFETs (or equivalent) connected as diodes across the TL03xA inputs as shown in Figure 65.

As with all precision applications, special care must be taken to eliminate external sources of leakage and interference. Other precautions include using high-quality insulation, cleaning insulating surfaces to remove fluxes and other residue, and enclosing the application within a protective box.

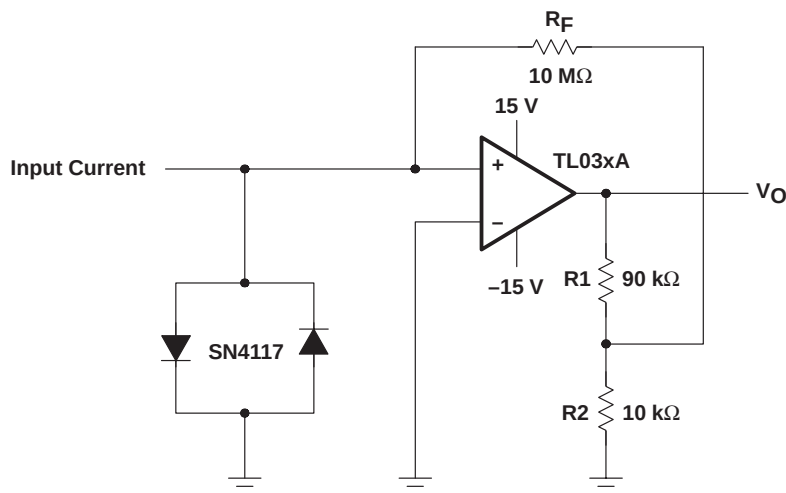


Figure 65. Transimpedance Amplifier

APPLICATION INFORMATION

4-mA to 20-mA current loops

Often, information from an analog sensor must be sent over a distance to the receiving circuitry. For many applications, the most feasible method involves converting voltage information to a current before transmission. The following circuits give two variations of low-power current loops. The circuit in Figure 66 requires three wires from the transmitting to receiving circuitry, while the second variation in Figure 67 requires only two wires, but includes an extra integrated circuit. Both circuits benefit from the high input impedance of the TL03xA because many inexpensive sensors do not have low output impedance.

Assuming that the voltage at the noninverting input of the TL03xA is zero, the following equation determines the output current:

$$I_O = V_I \left(\frac{R_3}{R_1 \times R_S} \right) + 5V \left(\frac{R_3}{R_2 \times R_S} \right) = 0.16 \times V_I + 4 \text{ mA}$$

The circuits presently provide 4-mA to 20-mA output current for an input voltage of 0 to 100 mV. By modifying R1, R2, and R3, the input voltage range or the output current range can be adjusted.

Including the offset voltage of the operational amplifier in the above equation clearly illustrates why the low offset TL03xA was chosen:

$$\begin{aligned} I_O &= V_I \left(\frac{R_3}{R_1 \times R_S} \right) + 5V \left(\frac{R_3}{R_2 \times R_S} \right) - V_I \left(\frac{R_3}{R_1 \times R_S} + \frac{R_3}{R_2 \times R_S} + \frac{R_1}{R_S} \right) \\ &= 0.16 \times V_I + 4 \text{ mA} - 0.17 \times V_I \end{aligned}$$

For example, an offset voltage of 1 mV decreases the output current by 0.17 mA.

Due to the low power consumption of the TL03xA, both circuits have at least 2 mA available to drive the actual sensor from the 5-V reference node.

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4-mA to 20-mA current loops (continued)

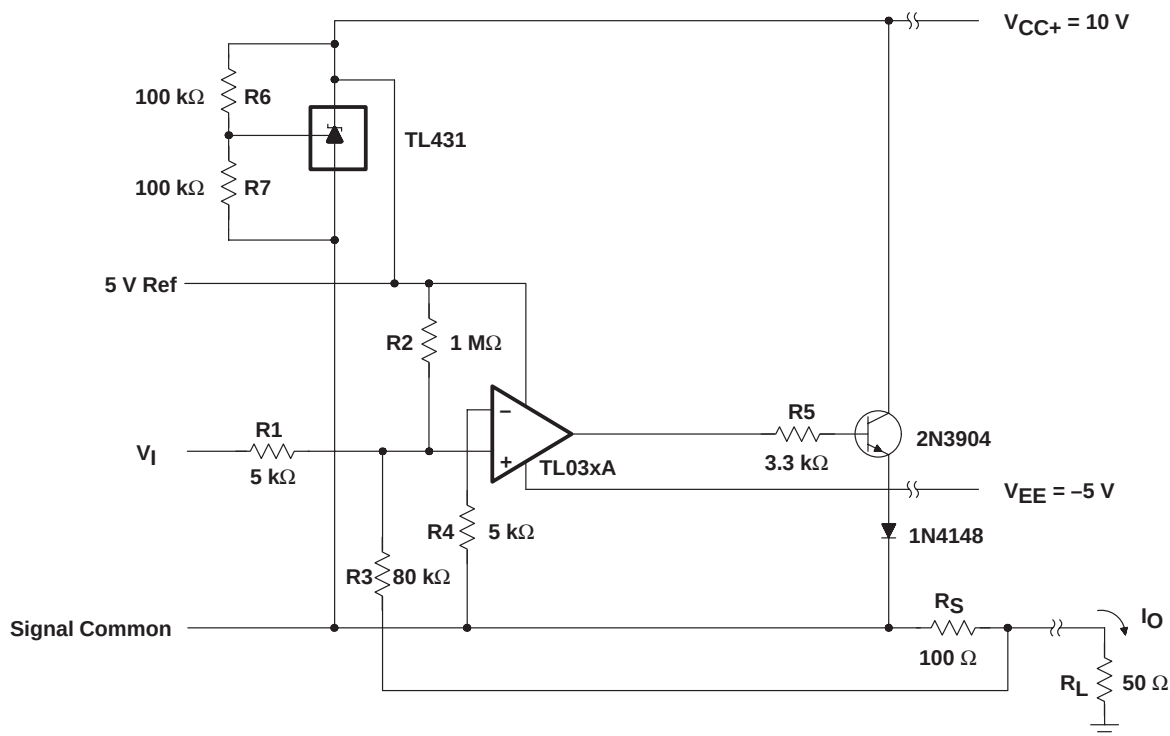


Figure 66. Three-Wire 4-mA to 20-mA Current Loop

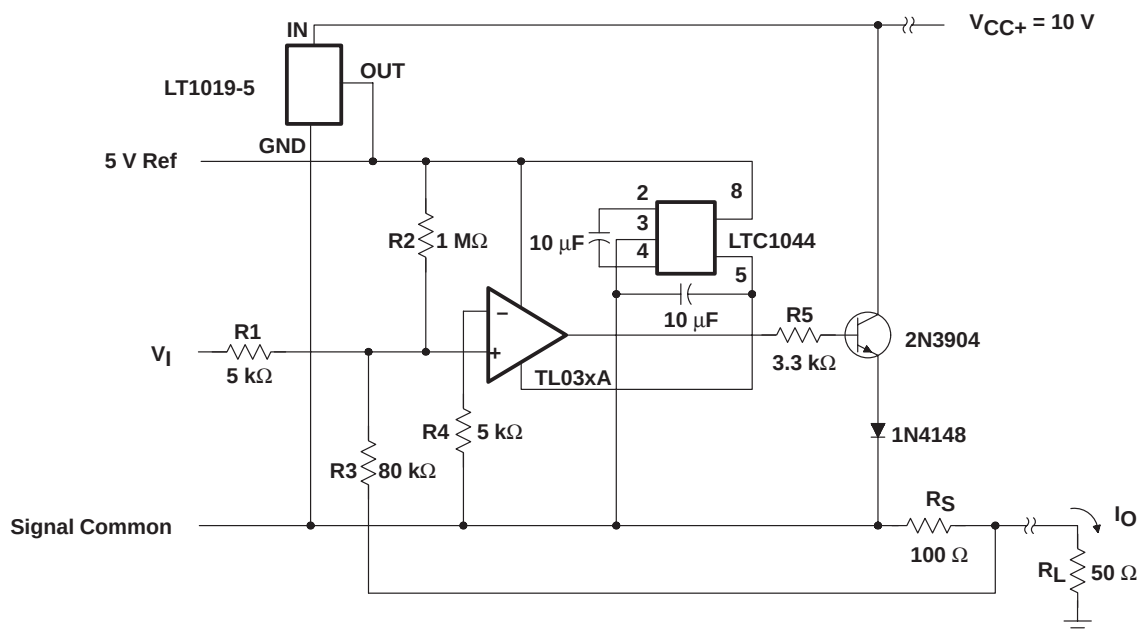


Figure 67. Two-Wire 4-mA to 20-mA Current Loop

APPLICATION INFORMATION

low-level light-detector preamplifier

Applications that need to detect small currents require high input-impedance operational amplifiers; otherwise, the bias currents of the operational amplifier camouflage the current being monitored. Phototransistors provide a current that is proportional to the light reaching the transistor. The TL03x allows even the small currents resulting from low-level light to be detected.

In Figure 68, if there is no light, the phototransistor is off and the output is high. As light is detected, the operational amplifier output begins pulling low. Adjusting R4 both compensates for offset voltage of the amplifier and adjusts the point of light detection by the amplifier.

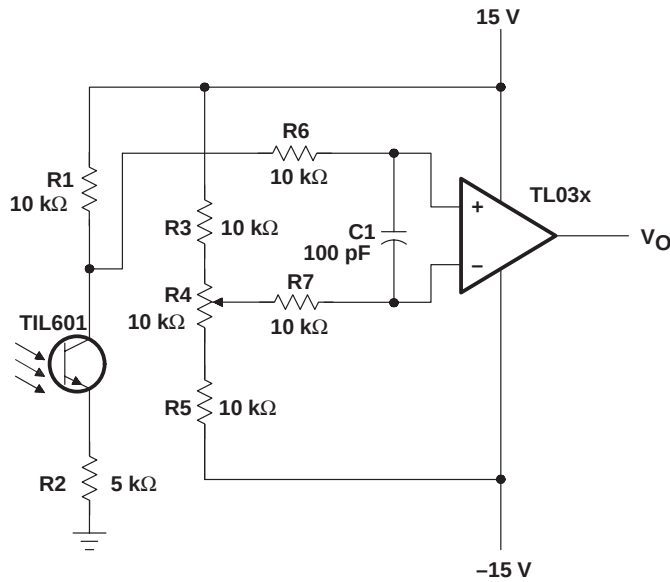


Figure 68. Low-Level Light-Detector Preamplifier

TL03x, TL03xA, TL03xY

ENHANCED-JFET LOW-POWER LOW-OFFSET

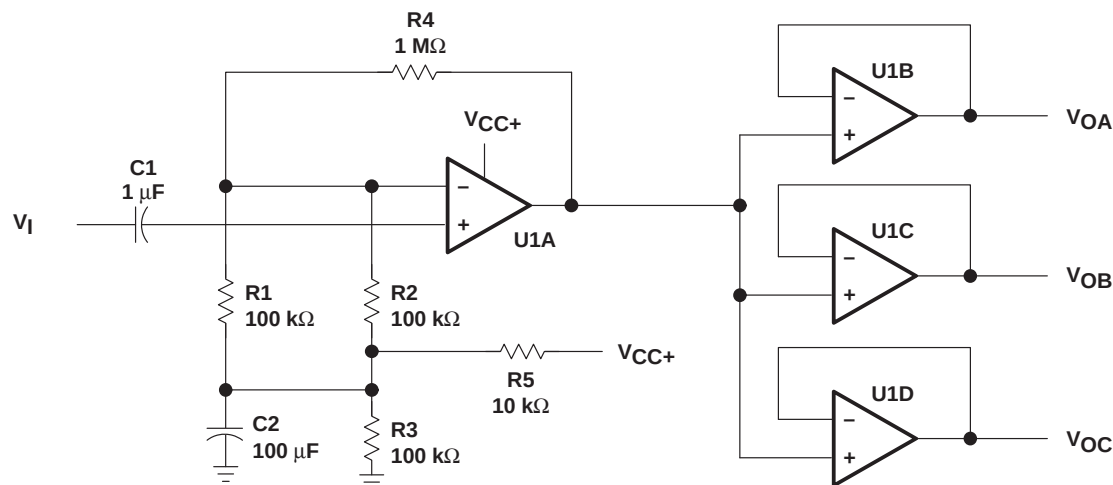
OPERATIONAL AMPLIFIERS

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APPLICATION INFORMATION

audio-distribution amplifier

This audio-distribution amplifier (see Figure 69) feeds the input signal to three separate output channels. U1A amplifies the input signal with a gain of 10, while U1B, U1C, and U1D serve as buffers to the output channels. The gain response of this circuit is very flat from 20 Hz to 20 kHz. The TL03x allows quick response to the input signal while maintaining low power consumption.



NOTE A: U1A through U1D = TL03x; $V_{CC+} = 5$ V.

Figure 69. Audio-Distribution Amplifier Circuit

instrumentation amplifier with linear gain adjust

$$V_O = \frac{R_6}{R_5} \times (V_B - V_A)$$

The diagram shows a four-op-amp instrumentation amplifier circuit. It has two input terminals, V_A and V_B , and one output terminal, V_O . The circuit is powered by V_{CC+} and V_{CC-} .

- Input Buffers:** Two op-amps, U1A and U1B, are configured as voltage followers. U1A's non-inverting input (+) is connected to V_A , and its inverting input (-) is connected to its output and V_{CC+} . Similarly, U1B's non-inverting input (+) is connected to V_B , and its inverting input (-) is connected to its output and V_{CC-} .
- Resistors:**
 - R_1 (10 k Ω , 0.1% tolerance) is connected between the output of U1A and a central node.
 - R_2 (10 k Ω , 0.1% tolerance) is connected between the output of U1B and the same central node.
 - R_3 (10 k Ω , 0.1% tolerance) is connected between the central node and ground.
 - R_4 (10 k Ω , 0.1% tolerance) is connected between the central node and the non-inverting input (+) of U1D.
 - R_5 (100 k Ω) is connected between the inverting input (-) of U1D and its output.
 - R_6 (1 M Ω) is connected between the output of U1C and the output V_O .
 - R_7 (100 k Ω) is connected between the output of U1D and ground.
- Differential Amplifier:**
 - Op-amp U1C is configured as a differential amplifier. Its non-inverting input (+) is connected to the central node, and its inverting input (-) is connected to the output of U1D. Its output is connected to V_O through resistor R_6 .
 - Op-amp U1D is configured as a differential amplifier. Its non-inverting input (+) is connected to the central node, and its inverting input (-) is connected to its output and V_{CC-} . Its output is connected to V_O through resistor R_6 and to ground through resistor R_7 .

NOTE A: U1A through U1D = TL03x; $V_{CC+} = \pm 15$ V.

Figure 70. Instrumentation Amplifier With Linear Gain-Adjust Circuit

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